Renesas

RX23W Group **Renesas MCUs**

Datasheet

R01DS0342EJ0120 Rev.1.20 Apr 20, 2023

54-MHz 32-bit RX MCUs, built-in FPU, 88.56 DMIPS, up to 512-KB flash memory, Bluetooth® 5.0, various communication functions including USB 2.0 full-speed host/function/OTG, CAN, SD host interface, serial sound interface, capacitive touch sensing unit, 12-bit A/D converter, 12-bit D/A converter, RTC, Encryption functions

Features

32-bit RXv2 CPU core

- Max. operating frequency: 54 MHz Capable of 88.56 DMIPS in operation at 54 MHz
- Enhanced DSP: 32-bit multiply-accumulate and 16-bit
- Built-in FPU: 32-bit single-precision floating point (compliant to primare) **IEEE754**)
- Divider (fastest instruction execution takes two CPU clock cycles) · Fast interrupt
- CISC Harvard architecture with 5-stage pipeline
- Variable-length instructions, ultra-compact code
- On-chip debugging circuit
- Memory protection unit (MPU) supported
- Low power design and architecture
 - Operation from a single 1.8-V to 3.6-V supply
 - RTC capable of operating on the battery backup power supply
 - Three low power consumption modes · Low power timer (LPT) that operates during the software standby state

On-chip flash memory for code • 384- to 512-Kbyte capacities

- On-board or off-board user programming
- Programmable at 1.8 V
- For instructions and operands

On-chip data flash memory

- 8 Kbytes (1,000,000 program/erase cycles (typ.))
- BGO (Background Operation)
- On-chip SRAM, no wait states

64-Kbyte size capacities

- Data transfer functions
 - DMAC: Incorporates four channels
- DTC: Four transfer modes
- ELC
 - Module operation can be initiated by event signals without using interrupts.
 - Linked operation between modules is possible while the CPU is sleeping.
- Reset and supply management
 - Eight types of reset, including the power-on reset (POR)
 Low voltage detection (LVD) with voltage settings

Clock functions

- Main clock oscillator frequency: 1 to 20 MHz
- · External clock input frequency: Up to 20 MHz
- Sub-clock oscillator frequency: 32.768 kHz
- Frequency of Bluetooth-dedicated clock oscillator: 32 MHz
- PLL circuit input: 4 MHz to 12.5 MHz
 On-chip low- and high-speed oscillators, dedicated on-chip low-speed oscillator for the IWDT
- USB-dedicated PLL circuit: 4, 6, 8, or 12 MHz 54 MHz can be set for the system clock and 48 MHz for the USB clock
- Generation of a dedicated 32.768-kHz clock for the RTC
- Clock frequency accuracy measurement circuit (CAC)

Realtime clock

- Adjustment functions (30 seconds, leap year, and error)
- Calendar count mode or binary count mode selectable
- Time capture function
- Time capture on event-signal input through external pins

Independent watchdog timer

15-kHz on-chip oscillator produces a dedicated clock signal to drive IWDT operation.

Useful functions for IEC60730 compliance

Self-diagnostic and disconnection-detection assistance functions for the A/D converter, clock frequency accuracy measurement circuit, independent watchdog timer, RAM test assistance functions using the DOC, etc.

Capacitive touch sensing unit

R01DS0342EJ0120 Rev.1.20

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- Self-capacitance method: A single pin configures a single key, supporting up to 12 keys
- · Mutual capacitance method: Matrix configuration with 12 pins, supporting up to 36 keys



Up to 12 communication functions

An RF transceiver and link layer compliant with the Bluetooth 5.0 Low Energy specification

LE 1M PHY, LE 2M PHY, LE Coded PHY (125 kbps and 500 kbps), And LE Advertising extension support On-chip Bluetooth-dedicated AES-CCM (128-bit blocks) encryption

circuit The 83-pin LGA product has been certified as compliant with radio-

related laws (in Japan, North America, and Europe). The 83-pin LGA product includes a small PCB trace antenna.

- USB 2.0 host/function/On-The-Go (OTG) (one channel),
- full-speed = 12 Mbps, low-speed = 1.5 Mbps, isochronous transfer, and BC (Battery Charger) supported
- CAN (one channel) compliant to ISO11898-1: Transfer at up to 1 Mbps
- SCI with many useful functions (up to 4 channels) Asynchronous mode, clock synchronous mode, smart card interface Reduction of errors in communications using the bit modulation function
- IrDA interface (one channel, in cooperation with the SCI5)
- I²C bus interface: Transfer at up to 400 kbps, capable of SMBus operation (one channel)
- RSPI (one channel): Transfer at up to 16 Mbps
- Serial sound interface (one channel)
- SD host interface (optional: one channel) SD memory/ SDIO 1-bit or 4-bit SD bus supported

Up to 19 extended-function timers

- 16-bit MTU: input capture, output compare, complementary PWM output, phase counting mode (five channels)
- 16-bit TPU: input capture, output compare, phase counting mode (six channels)
- 8-bit TMR (four channels)
- · 16-bit compare-match timers (four channels)

12-bit A/D converter

- Capable of conversion within 0.83 μs 14 channels
- · Sampling time can be set for each channel
- Self-diagnostic function and analog input disconnection detection assistance function
- 12-bit D/A converter

· Two channels

- Analog comparator Two channels × one unit
- General I/O ports
- · 5-V tolerant, open drain, input pull-up, switching of driving capacity
- Encryption functions (TSIP-Lite) · Unauthorized access to the encryption engine is disabled and
 - imposture and falsification of information are prevented · Safe management of keys
 - 128- or 256-bit key length of AES for ECB, CBC, GCM, others
- True random number generator

Temperature sensor

Operating temperature range

−40 to +85°C Applications

RENESAS

85-pin BGA, 56-pin QFN: General industrial and consumer equipment

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1. Overview

1.1 Outline of Specifications

 Table 1.1 lists the specifications, and Table 1.2 gives a comparison of the functions of the products in different packages.

Table 1.1 is for products with the greatest number of functions, so the number of peripheral modules and channels will differ in accordance with the package type. For details, see Table 1.2, Comparison of Functions for Different Packages.

Classification	Module/Function	Description				
CPU	CPU	 Maximum operating frequency: 54 MHz 32-bit RX CPU (RX v2) Minimum instruction execution time: One instruction per clock cycle Address space: 4-Gbyte linear Register set General purpose: Sixteen 32-bit registers Control: Ten 32-bit registers Accumulator: Two 72-bit registers Basic instructions: 75 (variable-length instruction format) Floating-point instructions: 11 DSP instructions: 23 Addressing modes: 10 Data arrangement Instructions: Little endian Data: Selectable as little endian or big endian On-chip 32-bit multiplier: 32-bit × 32-bit → 64-bit On-chip divider: 32-bit → 32 bits Barrel shifter: 32 bits Memory protection unit (MPU) 				
	FPU	 Single precision (32-bit) floating point Data types and floating-point exceptions in conformance with the IEEE754 standard 				
Memory	ROM	 Capacity: 384/512 Kbytes Up to 32 MHz: No-wait memory access 32 to 54 MHz: Wait state required. No wait state if the instruction is served by a ROM accelerator hit. Programming/erasing method: Serial programming (asynchronous serial communication/USB communication), self-programming 				
	RAM	Capacity: 64 Kbytes54 MHz, no-wait memory access				
	E2 DataFlash	Capacity: 8 KbytesNumber of erase/write cycles: 1,000,000 (typ)				
MCU operating mo	ode	Single-chip mode				
Clock	Clock generation circuit	 Main clock oscillator, sub-clock oscillator, low-speed on-chip oscillator, high-speed on-chip oscillator, PLL frequency synthesizer, USB-dedicated PLL frequency synthesizer, and IWDT-dedicated on-chip oscillator, Bluetooth-dedicated clock oscillator, Bluetooth-dedicated low-speed on-chip oscillator Oscillation stop detection: Available Clock frequency accuracy measurement circuit (CAC) Independent settings for the system clock (ICLK), peripheral module clock (PCLK), and FlashIF clock (FCLK) The CPU and system sections such as other bus masters run in synchronization with the system clock (ICLK): 54 MHz (at max.) MTU2a runs in synchronization with the PCLKA: 54 MHz (at max.) Peripheral modules other than MTU2a and S12ADE run in synchronization with the PCLKB: 32 MHz (at max.) The flash peripheral circuit runs in synchronization with the FCLK: 32 MHz (at max.) 				
Resets		RES# pin reset, power-on reset, voltage monitoring reset, watchdog timer reset, independent watchdog timer reset, and software reset				
Voltage detection	Voltage detection circuit (LVDAb)	 When the voltage on VCC falls below the voltage detection level, an internal reset or internal interrupt is generated. Voltage detection circuit 0 is capable of selecting the detection voltage from 3 levels Voltage detection circuit 1 is capable of selecting the detection voltage from 10 levels 				

Table 1.1Outline of Specifications (1/5)



Classification	Module/Function	Description					
Low power consumption	Low power consumption functions	 Module stop function Three low power consumption modes Sleep mode, deep sleep mode, and software standby mode Low power timer that operates during the software standby state 					
	Function for lower operating power consumption	 Operating power control modes High-speed operating mode, middle-speed operating mode, and low-speed operating mode 					
Interrupt	Interrupt controller (ICUb)	 Interrupt vectors: 148 External interrupts: 7 (NMI, IRQ0, IRQ1, IRQ4 to IRQ7 pins) Non-maskable interrupts: 6 (NMI pin, oscillation stop detection interrupt, voltage monitoring 1 interrupt, WDT interrupt, IWDT interrupt, and VBATT power monitoring interrupt) 16 levels specifiable for the order of priority 					
DMA	DMA controller (DMACA)	 4 channels Three transfer modes: Normal transfer, repeat transfer, and block transfer Activation sources: Software trigger, external interrupts, and interrupt requests from peripheral functions 					
	Data transfer controller (DTCa)	 Transfer modes: Normal transfer, repeat transfer, and block transfer Activation sources: Interrupts Chain transfer function 					
I/O ports	General I/O ports	85-pin/83-pin/56-pin • I/O: 43/43/29 • Input: 1/1/1 • Pull-up resistors: 43/43/29 • Open-drain outputs: 31/31/24 • 5-V tolerance: 3/3/2					
Event link control	ler (ELC)	 Event signals of 59 types can be directly connected to the module Operations of timer modules are selectable at event input Capable of event link operation for port B and port E 					
Multi-function pin	controller (MPC)	Capable of selecting the input/output function from multiple pins					
Timers	16-bit timer pulse unit (TPUa)	 (16 bits × 6 channels) × 1 unit Maximum of 10 pulse-input/output possible Select from among seven or eight counter-input clock signals for each channel Supports the input capture/output compare function Output of PWM waveforms in up to 9 phases in PWM mode Support for buffered operation, phase-counting mode (two-phase encoder input) and cascade connected operation (32 bits × 2 channels) depending on the channel. Capable of generating conversion start triggers for the A/D converters Signals from the input capture pins are input via a digital filter Clock frequency measuring method 					
	Multi-function timer pulse unit 2 (MTU2a)	 (16 bits × 5 channels) × 1 unit Up to 15 pulse-input/output lines are available based on the six 16-bit timer channels Select from among eight or seven counter-input clock signals for each channel (PCLK/1, PCLK/4, PCLK/16, PCLK/64, PCLK/256, PCLK/1024, MTCLKA, MTCLKB, MTCLKC, MTCLKD). Input capture function 18 output compare/input capture registers Pulse output mode Complementary PWM output mode Reset synchronous PWM mode Phase-counting mode Capable of generating conversion start triggers for the A/D converter 					
	Port output enable 2 (POE2a)	Controls the high-impedance state of the MTU's waveform output pins					
	Compare match timer (CMT)	 (16 bits × 2 channels) × 2 units Select from among four clock signals (PCLK/8, PCLK/32, PCLK/128, PCLK/512) 					
	Watchdog timer (WDTA)	 14 bits × 1 channel Select from among six counter-input clock signals (PCLK/4, PCLK/64, PCLK/128, PCLK/512, PCLK 2048, PCLK/8192) 					

Table 1.1Outline of Specifications (2/5)

Classification	Module/Function	Description
Timers	Independent watchdog timer (IWDTa)	 14 bits × 1 channel Count clock: Dedicated low-speed on-chip oscillator for the IWDT Frequency divided by 1, 16, 32, 64, 128, or 256
	Realtime clock (RTCe)	 Clock source: Sub-clock Time/calendar Interrupts: Alarm interrupt, periodic interrupt, and carry interrupt Time-capture facility for two values
	Low power timer (LPT)	 16 bits × 1 channel Clock source: Sub-clock, Dedicated low-speed on-chip oscillator for the IWDT Frequency divided by 2, 4, 8, 16, or 32
	8-bit timer (TMR)	 (8 bits × 2 channels) × 2 units Seven internal clocks (PCLK/1, PCLK/2, PCLK/8, PCLK/32, PCLK/64, PCLK/1024, and PCLK/8192) and an external clock can be selected Pulse output and PWM output with any duty cycle are available Two channels can be cascaded and used as a 16-bit timer
Communication functions	Serial communications interfaces (SCIg, SCIh)	 4 channels (channel 1, 5, 8: SCIg, channel 12: SCIh) SCIg Serial communications modes: Asynchronous, clock synchronous, and smart-card interface Multi-processor function On-chip baud rate generator allows selection of the desired bit rate Choice of LSB-first or MSB-first transfer Average transfer rate clock can be input from TMR timers for SCI5, and SCI12 Start-bit detection: Level or edge detection is selectable. Simple I²C Simple SPI 9-bit transfer mode Bit rate modulation Event linking by the ELC (only on channel 5) SCIh (The following functions are added to SCIg) Supports the serial communications protocol, which contains the start frame and information frame Supports the LIN format
	IrDA interface (IRDA)	 1 channel (SCI5 used) Supports encoding/decoding of waveforms conforming to IrDA standard 1.0
	I ² C bus interface (RIICa)	1 channel Communications formats: I ² C bus format/SMBus format Master mode or slave mode selectable Supports fast mode
	Serial peripheral interface (RSPIa)	 1 channel Transfer facility Using the MOSI (master out, slave in), MISO (master in, slave out), SSL (slave select), and RSPCK (RSPI clock) enables serial transfer through SPI operation (four lines) or clock-synchronous operation (three lines) Capable of handling serial transfer as a master or slave Data formats Choice of LSB-first or MSB-first transfer The number of bits in each transfer can be changed to 8, 9, 10, 11, 12, 13, 14, 15, 16, 20, 24, or 32 bits. 128-bit buffers for transmission and reception Up to four frames can be transmitted or received in a single transfer operation (with each frame having up to 32 bits) Double buffers for both transmission and reception
	USB 2.0 host/function module (USBc)	 USB Device Controller (UDC) and transceiver for USB 2.0 are incorporated. Host/function module: 1 port Compliant with USB version 2.0 Transfer speed: Full-speed (12 Mbps), low-speed (1.5 Mbps) OTG (ON-The-Go) is supported. Isochronous transfer is supported. BC1.2 (Battery Charging Specification Revision 1.2) is supported.
	CAN module (RSCAN)	 1 channel Compliance with the ISO11898-1 specification (standard frame and extended frame) 16 Message boxes

Table 1.1Outline of Specifications (3/5)

Classification	Module/Function	Description					
Communication	Serial Sound Interface (SSI)	• 1 channel					
functions		Capable of duplex communications					
		Various serial audio formats supported					
		 Master/slave function supported Programmable word clock or bit clock generation function 					
		 8/16/18/20/22/24/32-bit data formats supported 					
		On-chip 8-stage FIFO for transmission/reception					
		 Supports WS continue mode in which the SSIWS signal is not stopped. 					
	SD Host Interface (SDHIa)	• 1 channel					
		Transfer speed: Default speed mode (8MB/s)					
		 SD memory card interface (1 bit / 4bits SD bus) MMC, eMMC Backward-compatible are supported. 					
		SD Specifications					
		Part 1: Compliant with Physical Layer Specification Ver.3.01 (Not support DDR)					
		Part E1: SDIO Specification Ver. 3.00 • Error check function: CRC7 (command), CRC16 (data)					
		 Interrupt Source: Card access interrupt, SDIO access interrupt, Card detection interrupt, SD buffer 					
		access interrupt					
		DMA transfer sources: SD_BUF write, SD_BUF read Conditional Multiple protection					
		Card detection, Write protection					
	Bluetooth low energy (BLE)	 On-chip RF transceiver and link layer compliant with the Bluetooth 5.0 Low Energy specification Bit rates: 1 Mbps, 2 Mbps, 500 kbps, and 125 kbps 					
		LE Advertising extension support					
		• Includes an RF transceiver power supply (selectable as a DC-to-DC converter or linear regulator)					
		On-chip matching circuit to help reduce the number of external parts Transmission powers +4 dBm support					
		 Transmission power: +4 dBm support Small PCB trace antenna 					
		Certified as compliant with radio-related laws					
		Bluetooth-dedicated clock oscillator					
Encryption functior	ns	Access management circuit					
		• Encryption engine					
		128- or 256-bit key sizes of AES Block cipher mode of operation: GCM, ECB, CBC, CMAC, XTS, CTR, GCTR					
		Hash function					
		True random number generator					
		Prevention from illicit copying of a key					
12-bit A/D converte	er (S12ADE)	 12 bits (14 channels × 1 unit) 12-bit resolution 					
		 Minimum conversion time: 0.83 µs per channel when the ADCLK is operating at 54 MHz 					
		Operating modes					
		Scan mode (single scan mode, continuous scan mode, and group scan mode)					
		Group A priority control (only for group scan mode) Sampling variable 					
		Sampling time can be set up for each channel.					
		Self-diagnostic function					
		Double trigger mode (A/D conversion data duplicated)					
		 Detection of analog input disconnection A/D conversion start conditions 					
		 A/D conversion start conditions A software trigger, a trigger from a timer (MTU, TPU), an external trigger signal, or ELC 					
		• Event linking by the ELC					
Temperature sense	or (TEMPSA)	• 1 channel					
		 The voltage output from the temperature sensor is converted into a digital value by the 12-bit A/D converter. 					
12-bit D/A convert		2 channels					
12-bit D/A converte		2 channels 12-bit resolution					
		Output voltage: 0.4 to AVCC0-0.5V					
CRC calculator (C	RC)	CRC code generation for arbitrary amounts of data in 8-bit units					
,		 Select any of three generating polynomials: 					
		X ⁸ + X ² + X + 1, X ¹⁶ + X ¹⁵ + X ² + 1, or X ¹⁶ + X ¹² + X ⁵ + 1 • Generation of CRC codes for use with LSB-first or MSB-first communications is selectable.					
Companya D (C)							
Comparator B (CN	игра)	 2 channels × 1 unit Function to compare the reference voltage and the analog input voltage 					
		 Function to compare the reference voltage and the analog input voltage Window comparator operation or standard comparator operation is selectable 					
		Detection nin: 12 channels					
Capacitive touch s	ensing unit (CTSU)	Detection pin: 12 channels					
-		Comparison, addition, and subtraction of 16-bit data					
Data operation circ		-					

Table 1.1Outline of Specifications (4/5)



Classification	Module/Function	Description			
Packages		85-pin BGA (PTBG0085KB-A) 5.5 × 5.5 mm, 0.5 mm pitch			
		83-pin LGA (PTLG0083KA-A, PTLG0083KA-B) 6.1 × 9.5 mm, 0.5 mm pitch			
		56-pin QFN (PVQN0056LA-A) 7 × 7 mm, 0.4 mm pitch			
Debugging interfa	ices	FINE interface			

Table 1.1Outline of Specifications (5/5)



		RX23W Group				
Module/Functions		56 Pins	83 Pins	85 Pins		
External bus	External bus		Not supported			
Interrupts	External interrupts	NMI, IRQ0, IRQ1, IRQ4 to IRQ7				
DMA	DMA controller	4 ch	annels (DMAC0 to DM	AC3)		
	Data transfer controller		Available			
Timers	16-bit timer pulse unit	5 channels (TPU0 to TPU3, TPU5)	6 channels (1	PU0 to TPU5)		
	Multi-function timer pulse unit 2	5 c	hannels (MTU0 to MTU	J4)		
	Port output enable 2	POE0#, POE8#	POE0#, POE1#	, POE3#, POE8#		
	8-bit timer		2 channels × 2 units			
	Compare match timer		2 channels × 2 units			
	Low power timer		1 channel			
	Realtime clock		Available			
	Watchdog timer		Available			
	Independent watchdog timer		Available			
Communication functions	Serial communications interfaces (SCIg)	3 channels (SCI1, 5, 8)				
	IrDA interface	1 channel (SCI5)				
	Serial communications interfaces (SCIh)	Not supported 1 channel (SCI12		el (SCI12)		
	I ² C bus interface	1 channel				
	CAN module		1 channel			
	Serial peripheral interface	1 channel				
	USB 2.0 host/function module		1 channel			
	Serial sound interface	1 channel				
	SD Host Interface	Not supported 1 channel				
	Bluetooth low energy	An RF transceiver an	vith Bluetooth 5.0 low			
Capacitive touch sensing u	init	9 channels	12 ch	annels		
12-bit A/D converter (inclue	ling high-precision channels)	8 channels (4 channels)	14 channels (8 channels)			
Temperature sensor			Available			
D/A converter		1 channel	2 cha	annels		
CRC calculator			Available			
Event link controller			Available			
Comparator B			2 channels			
RF transceiver power supp	ly	DC-to-DC converter and linear regulator are selectable	Linear regulator	DC-to-DC converter and linear regulator are selectable		
Small PCB trace antenna		Not supported	Included	Not supported		
Dedicated crystal for the b	uetooth 32 MHz	Not supported	Included	Not supported		
Certificates of compliance standards, FCC, ISED, and	with radio-related laws (technical d CE)	—	Confirmed	_		
Packages		56-pin QFN	83-pin LGA	85-pin BGA		

Table 1.2 Comparison of Functions for Different Packages



1.2 List of Products

Table 1.3 is a list of products, and Figure 1.1 shows how to read the product part no., memory capacity, and package type.

Group	Part No.	Order Part No.	Package	ROM Capacity	RAM Capacity	E2 DataFlash	Operating Frequency	Security Function	Antenna	Operating Temperature
RX23W	R5F523W8ADBL	R5F523W8ADBL#20	PTBG0085KB-A	512 Kbytes	64 Kbytes	8 Kbytes	54 MHz	Not available	Not included	-40 to +85°C
	R5F523W8CDLN	R5F523W8CDLN#U0	PTLG0083KA-A					Not	Included	
		R5F523W8CDLN#20	PTLG0083KA-B					available		
	R5F523W8ADNG	R5F523W8ADNG#30	PVQN0056LA-A					Not available	Not included	
	R5F523W8BDBL	R5F523W8BDBL#20	PTBG0085KB-A					Available	Not included	
	R5F523W8DDLN	R5F523W8DDLN#U0	PTLG0083KA-A					Available	Included	
		R5F523W8DDLN#20	PTLG0083KA-B							
	R5F523W8BDNG	R5F523W8BDNG#30	PVQN0056LA-A					Available	Not included	
	R5F523W7ADBL	R5F523W7ADBL#20	PTBG0085KB-A	384 Kbytes	Ī			Not available	Not included	
	R5F523W7ADNG	R5F523W7ADNG#30	PVQN0056LA-A	1				Not available	Not included	
	R5F523W7BDBL	R5F523W7BDBL#20	PTBG0085KB-A					Available	Not included	1
	R5F523W7BDNG	R5F523W7BDNG#30	PVQN0056LA-A					Available	Not included	1

Table 1.3 List of Products: D Version (T_a = -40 to +85°C)



Figure 1.1 How to Read the Product Part Number



1.3 Block Diagram

Figure 1.2 shows a block diagram for the 85-pin BGA or 56-pin QFN product.



Figure 1.2 Block Diagram (85-Pin BGA, 56-Pin QFN)



Figure 1.3 shows a block diagram for the 83-pin LGA product.



Block Diagram (83-Pin LGA) Figure 1.3



1.4 Pin Functions

 Table 1.4 lists the pin functions.

Table 1.4Pin Functions (1/4)

Classifications	Pin Name	I/O	Description
Power supply	VCC	Input	Power supply pin. Connect it to the system power supply.
	VCL	_	Connect this pin to the VSS pin via a 4.7 μF smoothing capacitor used to stabilize the internal power supply. Place the capacitor close to the pin.
	VSS	Input	Ground pin. Connect it to the system power supply (0 V).
	VBATT	Input	Backup power pin
Clock	XTAL	Output	Pins for connecting a crystal. An external clock can be input through the
	EXTAL	Input	EXTAL pin.
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal between
	XCOUT	Output	XCIN and XCOUT.
	CLKOUT_RF	Output	Bluetooth-dedicated clock output pin for output of a 1-, 2-, or 4-MHz signal
	XTAL1_RF	Input	Pins for connecting the Bluetooth-dedicated clock oscillator. Connect a 32-
	XTAL2_RF	Output	MHz oscillator to these pins. The 83-pin LGA product includes a 32-MHz crystal resonator. XTAL1_RF and XTAL2_R should thus be externally connected to each other.
	CLKOUT	Output	Clock output pin.
Operating mode control	MD	Input	Pin for setting the operating mode. The signal levels on this pin must not be changed during operation.
	UB	Input	Pin used for boot mode (USB interface).
	UPSEL	Input	Pin used for boot mode (USB interface).
System control	RES#	Input	Reset pin. This MCU enters the reset state when this signal goes low.
CAC	CACREF	Input	Input pin for the clock frequency accuracy measurement circuit.
On-chip emulator	FINED	I/O	FINE interface pin.
Interrupts	NMI	Input	Non-maskable interrupt request pin.
	IRQ0, IRQ1, IRQ4 to IRQ7	Input	Interrupt request pins.
16-bit timer	TIOCB0	I/O	The TGRB0 inputs capture input/output compare output/PWM output pins.
pulse unit	TIOCB1	I/O	The TGRB1 inputs capture input/output compare output/PWM output pins.
	TIOCB2	I/O	The TGRB2 inputs capture input/output compare output/PWM output pins.
	TIOCA3, TIOCB3, TIOCC3, TIOCD3	I/O	The TGRA3 to TGRD3 input capture input/output compare output/PWM output pins.
	TIOCA4, TIOCB4	I/O	The TGRA4 and TGRB4 input capture input/output compare output/PWM output pins.
	TIOCB5	I/O	The TGRB5 inputs capture input/output compare output/PWM output pins.
	TCLKA, TCLKB, TCLKC, TCLKD	Input	Input pins for external clock signals.
Multi-function timer pulse unit 2	MTIOC0A, MTIOC0B, MTIOC0C	I/O	The TGRA0 to TGRC0 input capture input/output compare output/PWM output pins.
	MTIOC1A, MTIOC1B	I/O	The TGRA1 and TGRB1 input capture input/output compare output/PWM output pins.
	MTIOC2A, MTIOC2B	I/O	The TGRA2 and TGRB2 input capture input/output compare output/PWM output pins.
	MTIOC3A, MTIOC3B, MTIOC3C, MTIOC3D	I/O	The TGRA3 to TGRD3 input capture input/output compare output/PWM output pins.
	MTIOC4A, MTIOC4B, MTIOC4C, MTIOC4D	I/O	The TGRA4 to TGRD4 input capture input/output compare output/PWM output pins.
	MTCLKA, MTCLKB, MTCLKC, MTCLKD	Input	Input pins for the external clock.



Classifications	Pin Name	I/O	Description
Port output enable 2	POE0#, POE1#, POE3#, POE8#	Input	Input pins for request signals to place the MTU pins in the high impedance state.
Realtime clock	RTCOUT	Output	Output pin for the 1-Hz/64-Hz clock.
	RTCIC0, RTCIC1	Input	Time capture event input pins.
8-bit timer	TMO0 to TMO2	Output	Compare match output pins.
	TMCI0 to TMCI3	Input	Input pins for the external clock to be input to the counter.
	TMRI1 to TMRI3	Input	Counter reset input pins.
Serial	Asynchronous mode/clock s	synchrono	us mode
communications interface (SCIg)	SCK1, SCK5, SCK8	I/O	Input/output pins for the clock.
Internace (OCig)	RXD1, RXD5, RXD8	Input	Input pins for received data.
	TXD1, TXD5, TXD8	Output	Output pins for transmitted data.
	CTS1#, CTS5#, CTS8#	Input	Input pins for controlling the start of transmission and reception.
	RTS1#, RTS5#, RTS8#	Output	Output pins for controlling the start of transmission and reception.
	Simple I ² C mode		
	SSCL1, SSCL5, SSCL8	I/O	Input/output pins for the I ² C clock.
	SSDA1, SSDA5, SSDA8	I/O	Input/output pins for the I ² C data.
	Simple SPI mode		
	SCK1, SCK5, SCK8	I/O	Input/output pins for the clock.
	SMISO1, SMISO5, SMISO8	I/O	Input/output pins for slave transmit data.
	SMOSI1, SMOSI5, SMOSI8	I/O	Input/output pins for master transmit data.
	SS1#, SS5#, SS8#	Input	Slave-select input pins.
IrDA interface	IRTXD5	Output	Data output pin in the IrDA format.
	IRRXD5	Input	Data input pin in the IrDA format.
Serial	Asynchronous mode/clock s	synchrono	us mode
communications	SCK12	I/O	Input/output pin for the clock.
nterface (SCIh)	RXD12	Input	Input pin for receiving data.
	TXD12	Output	Output pin for transmitting data.
	CTS12#	Input	Input pin for controlling the start of transmission and reception.
	RTS12#	Output	Output pin for controlling the start of transmission and reception.
	Simple I ² C mode		
	SSCL12	I/O	Input/output pin for the I ² C clock.
	SSDA12	I/O	Input/output pin for the I ² C data.
	Simple SPI mode		
	SCK12	I/O	Input/output pin for the clock.
	SMISO12	I/O	Input/output pin for slave transmit data.
	SMOSI12	I/O	Input/output pin for master transmit data.
	SS12#	Input	Slave-select input pin.
	Extended serial mode	· ·	
	RXDX12	Input	Input pin for data reception by SCIf.
	TXDX12	Output	Output pin for data transmission by SCIf.
	SIOX12	1/0	Input/output pin for data reception or transmission by SCIf.
I ² C bus interface	SCL	I/O	Input/output pin for I ² C bus interface clocks. Bus can be directly driven b the N-channel open drain output.
	SDA	I/O	Input/output pin for I ² C bus interface data. Bus can be directly driven by the N-channel open drain output.

Table 1.4Pin Functions (2/4)

Classifications	Pin Name	I/O	Description
Serial peripheral	RSPCKA	I/O	Input/output pin for the RSPI clock.
interface	MOSIA	I/O	Input/output pin for transmitting data from the RSPI master.
	MISOA	I/O	Input/output pin for transmitting data from the RSPI slave.
	SSLA0	I/O	Input/output pin to select the slave for the RSPI.
	SSLA1, SSLA3	Output	Output pins to select the slave for the RSPI.
Serial sound	SSISCK0	I/O	SSI serial bit clock pin.
interface	SSIWS0	I/O	Word selection pin.
	SSITXD0	Output	Serial data output pin.
	SSIRXD0	Input	Serial data input pin.
	AUDIO_MCLK	Input	Master clock pin for audio.
CAN module	CRXD0	Input	Input pin
	CTXD0	Output	Output pin
SD host	SDHI_CLK	Output	SD clock output pin
interface	SDHI_CMD	I/O	SD command output, response input signal pin
	SDHI_D3 to SDHI_D0	I/O	SD data bus pins
	SDHI_CD	Input	SD card detection pin
	SDHI_WP	Input	SD write-protect signal
USB 2.0 host/ function module	VCC_USB	Input	Power supply pin for USB. Connect this pin to VCC or connect this pin to VSS via a 0.33 μF smoothing capacitor for stabilizing the internal power supply.
	VSS_USB	Input	Ground pin for USB. Connect this pin to VSS.
	USB0_DP	I/O	D+ I/O pin of the USB on-chip transceiver.
	USB0_DM	I/O	D- I/O pin of the USB on-chip transceiver.
	USB0_VBUS	Input	USB cable connection monitor pin.
	USB0_EXICEN	Output	Low-power control signal for the OTG chip.
	USB0_VBUSEN	Output	VBUS (5 V) supply enable signal for the OTG chip.
	USB0_OVRCURA, USB0_OVRCURB	Input	External overcurrent detection pins.
	USB0_ID	Input	Mini-AB connector ID input pin during operation in OTG mode.
12-bit A/D converter	AN000 to AN007, AN016 to AN020, AN027	Input	Input pins for the analog signals to be processed by the A/D converter.
	ADTRG0#	Input	Input pin for the external trigger signal that start the A/D conversion.
12-bit D/A converter	DA0, DA1	Output	Analog output pins of the D/A converter.
Comparator B	CMPB2, CMPB3	Input	Input pin for the analog signal to be processed by comparator B.
	CVREFB2, CVREFB3	Input	Analog reference voltage supply pin for comparator B.
	CMPOB2, CMPOB3	Output	Output pin for comparator B.
CTSU	TS2 to TS4, TS7, TS8, TS12, TS13, TS22, TS23, TS27, TS30, TS35	Output	Electrostatic capacitance measurement pins (touch pins).
	TSCAP	Output	LPF connection pin.
Analog power supply	AVCC0	Input	Analog voltage supply pin for the 12-bit A/D converter and D/A converter. Connect this pin to VCC when not using the 12-bit A/D converter and D/A converter.
	AVSS0	Input	Analog ground pin for the 12-bit A/D converter and D/A converter. Connect this pin to VSS when not using the 12-bit A/D converter and D/A converter
	VREFH0	Input	Analog reference voltage supply pin for the 12-bit A/D converter.
	VREFL0	Input	Analog reference ground pin for the 12-bit A/D converter.

Table 1.4Pin Functions (3/4)



Classifications	Pin Name	I/O	Description
I/O ports	P03, P05, P07	I/O	3-bit input/output pins.
	P14 to P17	I/O	4-bit input/output pins.
	P21, P22, P25 to P27	I/O	5-bit input/output pins.
	P30, P31, P35 to P37	I/O	5-bit input/output pins (P35 input pin).
	P40 to P47	I/O	8-bit input/output pins.
	PB0, PB1, PB3, PB5, PB7	I/O	5-bit input/output pins.
	PC0, PC2 to PC7	I/O	7-bit input/output pins.
	PD3	I/O	1-bit input/output pins.
	PE0 to PE4	I/O	5-bit input/output pins.
	PJ3	I/O	1-bit input/output pin.
Bluetooth low energy	ANT	I/O	RF single I/O pin for RF transceiver Set the impedance of the signal line to 50 Ω .
	INT_ANT	I/O	Internal antenna connection pin Externally connect this pin to the ANT pin.
	DCLOUT	Output	RF transceiver power-supply output pin
	DCLIN_A, DCLIN_D	Input	RF transceiver power-supply output connection pin In the case of an 83-pin LGA product, these pins should be externally connected to the DCLOUT pin.
	VCC_RF	Input	RF transceiver power supply pin
	AVCC_RF	Input	RF transceiver power supply pin
	VSS_RF	Input	RF transceiver ground pin

Table 1.4Pin Functions (4/4)



1.5 Pin Assignments

1.5.1 85-Pin BGA



Figure 1.4 Pin Assignments of the 85-Pin BGA

1.5.2 83-Pin LGA

	RX23W Group PTLG0083KA-A PTLG0083KA-B (83-pin LGA) (Upper perspective view)
31 30 29 32 64 63 33 65 63 34 66 66 35 67 68 36 68 37 69 38 70 9 71	
40 72 41 1 2 3	
MD RES# XCIN P35 XCOUT P31 P37/ XTAL P30 P36/ EXTAL P27	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

Figure 1.5 Pin Assignments of the 83-Pin LGA



1.5.3 56-Pin QFN



Figure 1.6 Pin Assignments of the 56-Pin QFN



1.6 List of Pins and Pin Functions

1.6.1 85-Pin BGA

Table 1.5 List of Pins and Pin Functions (85-Pin BGA) (1/2)

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TPU, TMR, RTC, CMT, POE, CAC)	Communications (SCI, RSPI, RIIC, RSCAN, USB, SSI)	Memory Interface (SDHI)	Touch sensing	Others
A1		P25	MTIOC4C/MTCLKB/TIOCA4			TS4	ADTRG0#
A2		P30	MTIOC4B/TMRI3/POE8#/ RTCIC0	RXD1/SMISO1/SSCL1/ AUDIO_MCLK			IRQ0/CMPOB3
A3	VCC						
A4	EXTAL	P36					
A5	VSS						
A6	XTAL	P37					
A7	XCOUT						
A8	XCIN						
A9	VCL						
A10	AVSS0						
B1		P17	MTIOC3A/MTIOC3B/TMO1/ POE8#/TIOCB0/TCLKD	SCK1/MISOA/SDA/SSITXD0			IRQ7/CMPOB2
B2		P26	MTIOC2A/TMO1	TXD1/SMOSI1/SSDA1/SSIRXD0/ USB0_VBUSEN		TS3	CMPB3
B3		P27	MTIOC2B/TMCI3	SCK1/SSIWS0		TS2	CVREFB3
B4		P31	MTIOC4D/TMCI2/RTCIC1 CTS1#/RTS1#/SSISCK0				IRQ1
B5	UPSEL	P35				NMI	
B6	RES#						
B7	MD						FINED
B8		P03					DA0
B9		P05					DA1
B10	AVCC0						
C1		P14	MTIOC3A/MTCLKA/TMRI2/ TIOCB5/TCLKA	CTS1#/RTS1#/SS1#/CTXD0/ USB0_OVRCURA		TS13	IRQ4/ CVREFB2
C2		P15	MTIOC0B/MTCLKB/TMCI2/ TIOCB2/TCLKB	RXD1/SMISO1/SSCL1/CRXD0		TS12	IRQ5/CMPB2
C3		P16	MTIOC3C/MTIOC3D/TMO2/ TIOCB1/TCLKC/RTCOUT	TXD1/SMOSI1/SSDA1/MOSIA/SCL/ USB0_VBUS/USB0_VBUSEN/ USB0_OVRCURB			IRQ6/ ADTRG0#
C4		P22	MTIOC3B/MTCLKC/TMO0/ TIOCC3	USB0_OVRCURB/AUDIO_MCLK		TS7	
C5	VBATT						
C6		PJ3	MTIOC3C				
C7		P07					ADTRG0#
C8		P41					AN001
C9		P40					AN000
C10	VREFH0						
D1				USB0_DM			
D2	VCC_USB						
D3		P21	MTIOC1B/TMCI0/TIOCA3	USB0_EXICEN/SSIWS0		TS8	
D4	VSS_RF						
D8		P42					AN002
D9		P43					AN003
D10	VREFL0						
E1				USB0_DP			
E2	VSS_USB						
E3	VSS_RF						
E8		P46					AN006
E9		P45					AN005
E10		P44					AN004
F1	UB	PC7	MTIOC3A/MTCLKB/TMO2	TXD8/SMOSI8/SSDA8/MISOA			CACREF



Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TPU, TMR, RTC, CMT, POE, CAC)	Communications (SCI, RSPI, RIIC, RSCAN, USB, SSI)	Memory Interface (SDHI)	Touch sensing	Others
2		PC6	MTIOC3C/MTCLKA/TMCI2	RXD8/SMISO8/SSCL8/MOSIA/ USB0_EXICEN		TS22	
-3	VSS_RF						
8	VSS_RF						
-9		PD3	POE8#				AN027
10		P47					AN007/ CLKOUT_RF
3 1		PC4	MTIOC3D/MTCLKC/TMCI1/ POE0#	CTS8#/RTS8#/SS8#/SSLA0/SCK5	SDHI_D1	TSCAP	
62		PC5	MTIOC3B/MTCLKD/TMRI2	SCK8/RSPCKA/USB0_ID		TS23	
33	VSS_RF						
68	VSS_RF						
3 9		PE0		SCK12			AN016
G10	DCLIN_A						
11	_	PC3	MTIOC4D/TCLKB	TXD5/SMOSI5/SSDA5/IRTXD5	SDHI D0	TS27	
12		PC2	MTIOC4B/TCLKA	RXD5/SMISO5/SSCL5/SSLA3/ IRRXD5	SDHI_D3	TS30	
13	VSS_RF						
14		PB3	MTIOC0A/MTIOC4A/TMO0/ POE3#/TIOCD3/TCLKD		SDHI_WP		
15	VSS_RF						
16	VSS_RF						
17	VSS_RF						
18	_	PE3 MTIOC4B/POE8# CTS12#/RTS12#/SS12#/ AUDIO_MCLK				AN019/ CLKOUT	
19		PE2	MTIOC4A	RXD12/RXDX12/SMISO12/SSCL12			IRQ7/AN018
110	DCLIN D						
1	_	PC0	MTIOC3C/TCLKC	CTS5#/RTS5#/SS5#/SSLA1		TS35	
2	VSS_RF						
3	_	PB7	MTIOC3B/TIOCB5		SDHI D2		
4		PB5	MTIOC2A/MTIOC1B/TMRI1/ POE1#/TIOCB4	USB0_VBUS	SDHI_CD		
15		PB1	MTIOC0C/MTIOC4C/TMCI0/ TIOCB3		SDHI_CLK		IRQ4
6		PB0	TIOCA3	RSPCKA	SDHI_CMD		
7	VSS_RF				_		
8		PE4	MTIOC4D/MTIOC1A				AN020/ CLKOUT
19		PE1	MTIOC4C	TXD12/TXDX12/SIOX12/SMOSI12/ SSDA12			AN017
10	VCC_RF						
(1	VSS_RF						
(2							ANT
(3	VSS_RF						
(4	VCC						
(5	VSS	1		1	1	1	ł
(6	XTAL2_RF					1	
(7	 XTAL1_RF					1	
(8	 AVCC_RF					1	
(9	DCLOUT						
(10	VSS_RF				1	+	

Table 1.5 List of Pins and Pin Functions (85-Pin BGA) (2/2)

1.6.2 83-Pin LGA

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TPU, TMR, RTC, CMT, POE, CAC)	Communications (SCI, RSPI, RIIC, RSCAN, USB, SSI)	Memory Interface (SDHI)	Touch sensing	Others
1		P22	MTIOC3B/MTCLKC/TMO0/ TIOCC3	USB0_OVRCURB/AUDIO_MCLK		TS7	
2		P21	MTIOC1B/TMCI0/TIOCA3	USB0_EXICEN/SSIWS0		TS8	
3	VCC_USB						
4				USB0_DM			
5				USB0_DP			
6	VSS_USB						
7		PC5	MTIOC3B/MTCLKD/TMRI2	SCK8/RSPCKA/USB0_ID		TS23	
8		PC3	MTIOC4D/TCLKB	TXD5/SMOSI5/SSDA5/IRTXD5	SDHI_D0	TS27	
9	VSS_RF						
10							ANT
11							INT_ANT
12	VSS_RF						
13	VSS_RF						
14	VSS_RF						
15	VSS_RF						
16	VSS_RF						
17	VSS_RF						
18	VSS_RF						
19	VSS_RF						
20	VSS_RF						
21		PE1	MTIOC4C	TXD12/TXDX12/SIOX12/SMOSI12/ SSDA12			AN017
22		PE0		SCK12			AN016
23		P45					AN005
24		P47					AN007/ CLKOUT_RF
25		P43					AN003
26	VREFL0						
27	VREFH0						
28	AVCC0						
29	AVSS0						
30	VSS						
31	VCC						
32		P03					DA0
33	VCL						
34	MD						FINED
35	XCIN						
36	XCOUT						
37	XTAL	P37					
38	EXTAL	P36					
39	VBATT						
40		P25	MTIOC4C/MTCLKB/TIOCA4			TS4	ADTRG0#
41		P16	MTIOC3C/MTIOC3D/TMO2/ TIOCB1/TCLKC/RTCOUT	TXD1/SMOSI1/SSDA1/MOSIA/SCL/ USB0_VBUS/USB0_VBUSEN/ USB0_OVRCURB			IRQ6/ ADTRG0#
42		P15	MTIOC0B/MTCLKB/TMCI2/ TIOCB2/TCLKB	RXD1/SMISO1/SSCL1/CRXD0		TS12	IRQ5/CMPB2
43		P14	MTIOC3A/MTCLKA/TMRI2/ TIOCB5/TCLKA	CTS1#/RTS1#/SS1#/CTXD0/ USB0_OVRCURA		TS13	IRQ4/ CVREFB2
44	UB	PC7	MTIOC3A/MTCLKB/TMO2	TXD8/SMOSI8/SSDA8/MISOA			CACREF
45		PC6	MTIOC3C/MTCLKA/TMCI2	RXD8/SMISO8/SSCL8/MOSIA/ USB0_EXICEN		TS22	
46		PC4	MTIOC3D/MTCLKC/TMCI1/ POE0#	CTS8#/RTS8#/SS8#/SSLA0/SCK5	SDHI_D1	TSCAP	

Table 1.6 List of Pins and Pin Functions (83-Pin LGA) (1/2)



Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TPU, TMR, RTC, CMT, POE, CAC)	Communications (SCI, RSPI, RIIC, RSCAN, USB, SSI)	Memory Interface (SDHI)	Touch sensing	Others
47		PC0	MTIOC3C/TCLKC	CTS5#/RTS5#/SS5#/SSLA1		TS35	
48		PC2	MTIOC4B/TCLKA	RXD5/SMISO5/SSCL5/SSLA3/ IRRXD5	SDHI_D3	TS30	
49		PB7	MTIOC3B/TIOCB5		SDHI_D2		
50		PB5	MTIOC2A/MTIOC1B/TMRI1/ POE1#/TIOCB4	USB0_VBUS	SDHI_CD		
51		PB3	MTIOC0A/MTIOC4A/TMO0/ POE3#/TIOCD3/TCLKD		SDHI_WP		
52		PB1	MTIOC0C/MTIOC4C/TMCI0/ TIOCB3		SDHI_CLK		IRQ4
53		PB0	TIOCA3	RSPCKA	SDHI_CMD		
54		PE4	MTIOC4D/MTIOC1A				AN020/ CLKOUT
55		PE3	MTIOC4B/POE8#	CTS12#/RTS12#/SS12#/ AUDIO_MCLK			AN019/ CLKOUT
56		PE2	MTIOC4A RXD12/RXDX12/SMISO12/SSCL12				IRQ7/AN018
57		PD3	POE8#				AN027
58		P46					AN006
59		P44					AN004
60		P42					AN002
61		P41					AN001
62		P40					AN000
63		P07					ADTRG0#
64		P05					DA1
65		PJ3	MTIOC3C				
66	RES#						
67	UPSEL	P35					NMI
68		P31	MTIOC4D/TMCI2/RTCIC1	CTS1#/RTS1#/SS1#/SSISCK0			IRQ1
69		P30	MTIOC4B/TMRI3/POE8#/ RTCIC0	RXD1/SMISO1/SSCL1/ AUDIO_MCLK			IRQ0/CMPOB3
70		P27	MTIOC2B/TMCI3	SCK1/SSIWS0		TS2	CVREFB3
71		P26	MTIOC2A/TMO1	TXD1/SMOSI1/SSDA1/SSIRXD0/ USB0_VBUSEN		TS3	CMPB3
72		P17	MTIOC3A/MTIOC3B/TMO1/ POE8#/TIOCB0/TCLKD	SCK1/MISOA/SDA/SSITXD0			IRQ7/CMPOB2
73	VSS_RF						
74	XTAL1_RF						
75	XTAL2_RF						
76	DCLOUT						
77	DCLIN_D						
78	DCLIN_A						
79	VSS_RF						
80	VSS_RF						
81	VSS_RF						
82	VSS_RF						
83	VSS_RF						

Table 1.6 List of Pins and Pin Functions (83-Pin LGA) (2/2)

1.6.3 56-Pin QFN

Table 1.7 List of Pins and Pin Functions (56-Pin QFN) (1/2)

Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TPU, TMR, RTC, CMT, POE, CAC)	Communications (SCI, RSPI, RIIC, RSCAN, USB, SSI)	Touch sensing	Others
1	VCL					
2	MD					FINED
6	XCIN					
	XCOUT					
5	RES#					
i	XTAL	P37				
,	VSS					
;	EXTAL	P36				
)	VCC					
0	UPSEL	P35				NMI
1		P31	MTIOC4D/TMCI2/RTCIC1	CTS1#/RTS1#/SS1#/SSISCK0		IRQ1
2		P30	MTIOC4B/TMRI3/POE8#/RTCIC0	RXD1/SMISO1/SSCL1/AUDIO_MCLK		IRQ0/CMPOB3
3		P27	MTIOC2B/TMCI3	SCK1/SSIWS0	TS2	CVREFB3
4		P26	MTIOC2A/TMO1	TXD1/SMOSI1/SSDA1/SSIRXD0/ USB0_VBUSEN	TS3	CMPB3
5		P17	MTIOC3A/MTIOC3B/TMO1/POE8#/ TIOCB0/TCLKD	SCK1/MISOA/SDA/SSITXD0		IRQ7/CMPOB2
16		P16 MTIOC3C/MTIOC3D/TMO2/TIOCB1/ TXD1/SMOSI1/SSDA1/MOSIA/SCL/ TCLKC/RTCOUT USB0_VBUS/USB0_VBUSEN/ USB0_OVRCURB			IRQ6/ADTRG0#	
17		P15 MTIOC0B/MTCLKB/TMCI2/TIOCB2/ RXD1/SMISO1/SSCL1/CRXD0 TCLKB		TS12	IRQ5/CMPB2	
8		P14	MTIOC3A/MTCLKA/TMRI2/TIOCB5/ TCLKA	CTS1#/RTS1#/SS1#/CTXD0/ USB0_OVRCURA	TS13	IRQ4/CVREFB2
9	VCC_USB					
20				USB0_DM		
1				USB0_DP		
2	VSS_USB					
3	UB	PC7	MTIOC3A/MTCLKB/TMO2	TXD8/SMOSI8/SSDA8/MISOA		CACREF
.4		PC6	MTIOC3C/MTCLKA/TMCI2	RXD8/SMISO8/SSCL8/MOSIA/ USB0_EXICEN	TS22	
25		PC5	MTIOC3B/MTCLKD/TMRI2	SCK8/RSPCKA/USB0 ID	TS23	
6		PC4	MTIOC3D/MTCLKC/TMCI1/POE0#	 CTS8#/RTS8#/SS8#/SSLA0/SCK5	TSCAP	
7		PC3	MTIOC4D/TCLKB	TXD5/SMOSI5/SSDA5/IRTXD5	TS27	
8	VSS_RF					
9	_	PC2	MTIOC4B/TCLKA	RXD5/SMISO5/SSCL5/SSLA3/IRRXD5	TS30	
0		PC0	MTIOC3C/TCLKC	CTS5#/RTS5#/SS5#/SSLA1	TS35	
1		PB7	МТІОСЗВ/ТІОСВ5			
2						ANT
33		PB1	MTIOC0C/MTIOC4C/TMCI0/TIOCB3			IRQ4
34 34	VCC					
35		PB0	TIOCA3	RSPCKA		
36	VSS					
57	XTAL2_RF	+		1		
8	XTAL2_R					
9	AVCC_RF					
.0	DCLOUT	+		1		
1	201001	PE4	MTIOC4D/MTIOC1A			AN020/CLKOU
2		PE3	MTIOC4B/POE8#	AUDIO_MCLK		AN020/CLKOU
.3		PE3 PE2	MTIOC4A			IRQ7/AN018
	VCC PE	F ĽZ				
4	VCC_RF DCLIN_D					
-5	DCLIN_D					
6						



Pin No.	Power Supply, Clock, System Control	I/O Port	Timers (MTU, TPU, TMR, RTC, CMT, POE, CAC)	Communications (SCI, RSPI, RIIC, RSCAN, USB, SSI)	Touch sensing	Others
48		P47				AN007/ CLKOUT_RF
49		P46				AN006
50		P45				AN005
51		P41				AN001
52	VREFL0					
53	VREFH0					
54	AVCC0					
55		P05				DA1
56	AVSS0					

Table 1.7List of Pins and Pin Functions (56-Pin QFN) (2/2)

Note: VSS_RF is assigned as the exposed die pad. For details, refer to Appendix 2, Package Dimensions.



2. Electrical Characteristics

2.1 Absolute Maximum Ratings

Table 2.1 Absolute Maximum Ratings

Conditions: VSS = AVSS0 = VREFL0 = VSS_USB = VSS_RF = 0 V

	Item	Symbol	Value	Unit
Power supply vo	oltage	VCC, VCC_USB	-0.3 to +4.0	V
VBATT power s	upply voltage	VBATT	-0.3 to +4.0	V
Input voltage	Ports for 5 V tolerant*1	V _{in}	-0.3 to +6.5	V
	P03, P05, P07, P40 to P47		-0.3 to AVCC0 + 0.3	
	ANT		-1.0 to +1.4	
	XTAL1_RF, XTAL2_RF		-0.3 to +1.4	
	DCLIN_A, DCLIN_D		-0.3 to +2.2	
	Ports other than above*2		-0.3 to VCC + 0.3	
Reference powe	er supply voltage	VREFH0	-0.3 to AVCC0 + 0.3	V
Analog power s	upply voltage	AVCC0	-0.3 to +4.0	V
		VCC_RF	-0.3 to +4.0	V
		AVCC_RF	-0.3 to +4.0	V
Analog input	When AN000 to AN007 are used	V _{AN}	-0.3 to AVCC0 + 0.3	V
voltage	When AN016 to AN020, AN027 are used		-0.3 to VCC + 0.3	
Operating temp	erature	T _{opr}	-40 to +85	°C
Storage tempera	ature	T _{stg}	–55 to +125	°C

Caution: Permanent damage to the MCU may be caused if absolute maximum ratings are exceeded.

To preclude any malfunctions due to noise interference, insert capacitors with high frequency characteristics between the VCC and VSS pins, between the AVCC0 and AVSS0 pins, between the VCC_USB and VSS_USB pins, between the VREFH0 and VREFL0 pins, between the VCC_RF and VSS_RF pins, and between the AVCC0_RF and VSS_RF pins. Place capacitors with values of about 2.2 μ F in the case of the VCC_RF pin and about 0.1 μ F otherwise as close as possible to every power supply pin, and use the shortest and thickest possible traces for the connections.

Connect the VCL pin to a VSS pin via a 4.7 µF capacitor. The capacitor must be placed close to the pin. For details, refer to section 2.16.1, Connecting VCL Capacitor and Bypass Capacitors.

Do not input signals or an I/O pull-up power supply to ports other than 5-V tolerant ports while the device is not powered. The current injection that results from input of such a signal or I/O pull-up may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Even if -0.3 to +6.5 V is input to 5-V tolerant ports, it will not cause problems such as damage to the MCU.

Note 1. P16, P17, and PB5 are 5 V tolerant.

Note 2. When the VBATT power supply is selected, P30, P31 are rated from -0.3 V to VBATT + 0.3 V.



ltem	Symbol	Conditions	Min.	Тур.	Max.	Unit
Power supply voltages	VCC*1, *2, *3	When USB is not used	1.8	—	3.6	V
		When USB is used	3.0	—	3.6	
	VSS		—	0	—	
USB power supply voltages	VCC_USB	When USB regulator is not used	—	VCC	—	V
	VSS_USB		—	0	—	
VBATT power supply voltage	VBATT		1.8	—	3.6	V
Analog power supply voltages	AVCC0*1, *2		1.8	—	3.6	V
	AVSS0		_	0	—	
	VREFH0		1.8	—	AVCC0	
	VREFL0		_	0	—	
BLE power supply voltages	VCC_RF ^{*3}		1.8	—	3.6	V
	AVCC_RF*3		1.8	—	3.6	
	VSS_RF		—	0	—	

Table 2.2 Recommended Operating Voltage Conditions

Note 1. P41 and P47: Set AVCC0 to the same voltage as VCC.

If conditions other than those above are applicable, those listed below apply.

While VCC > 2.4 V: AVCC and VCC can be set independently when AVCC0 ≥ 2.4 V

While VCC ≤ 2.4 V: AVCC and VCC can be set independently when AVCC0 ≥ VCC

Note 2. When powering on the VCC and AVCC0 pins, power them on at the same time or the VCC pin first and then the AVCC0 pin.

Note 3. Set VCC_RF and AVCC_RF to the same voltage as VCC.



2.2 DC Characteristics

Table 2.3DC Characteristics (1) (1/2)

Conditions: $2.7 V \le VCC = VCC_USB = VCC_RF = AVCC_RF \le 3.6 V, 2.7 V \le AVCC0 \le 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C$

	Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Schmitt trigger input voltage	RIIC input pin (except for SMB	us, 5 V tolerant)	V _{IH}	VCC × 0.7	_	5.8	V	
	P16, P17, PB5 (5 V tolerant)			VCC × 0.8	_	5.8		
	P14, P15, P21, P22, P25 to P27, P35 to P37, PB0, PB1, PB3, PB7, PC0, PC2 to PC7, PD3, PE0 to PE4, PJ3, P30, P31 (other than RTCICn pin), RES#			VCC × 0.8	_	VCC + 0.3		
	P03, P05, P07, F	240 to P47		AVCC0 × 0.8	_	AVCC0 + 0.3		
	P30, P31 (RTCICn pin)	When VCC is supplied		VCC × 0.8	_	VCC + 0.3		
		When VBATT is supplied		VBATT × 0.8	—	VBATT + 0.3		
	RIIC input pin (ex	cept for SMBus)	V _{IL}	-0.3	—	VCC × 0.3		
	P14 to P17, P21, P22, P25 to P35 to P37, PB0, PB1, PB3, I PC0, PC2 to PC7 PD3, PE0 to PE4, PJ3, P30, P31 (other than RTCI RES#	PB5, PB7, 7,		-0.3	_	VCC × 0.2		
	P03, P05, P07, F	240 to P47		-0.3	_	AVCC0 × 0.2		
	P30, P31 (RTCICn pin)	When VCC is supplied		-0.3	_	VCC × 0.3		
		When VBATT is supplied		-0.3	_	VBATT × 0.3		
Schmitt trigger input voltage	RIIC input pin (ex P16, P17, PB5	cept for SMBus),	ΔV _T	VCC × 0.05		_	V	
	P14, P15, P21, P22, P25 to P35 to P37, PB0, PB1, PB3, PC0, PC2 to PC7 PD3, PE0 to PE4, PJ3, P30, P31 (other than RTCI RES#	PB7, 7,		VCC × 0.1	_	_		
	P03, P05, P07, F	240 to P47		AVCC0 × 0.1	_	_	1	



Table 2.3DC Characteristics (1) (2/2)Conditions: $2.7 V \le VCC = VCC_USB = VCC_RF = AVCC_RF \le 3.6 V, 2.7 V \le AVCC0 \le 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C$

	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Input level	MD	V _{IH}	VCC × 0.9	_	VCC + 0.3	V	
voltage (except for Schmitt	EXTAL (external clock input)		VCC × 0.8	_	VCC + 0.3		
trigger input	RIIC input pin (SMBus)		2.1	_	VCC + 0.3		
pins)	MD	V _{IL}	-0.3	_	VCC × 0.1		
	EXTAL (external clock input)		-0.3	_	VCC × 0.2		
	RIIC input pin (SMBus)]	-0.3	_	0.8		



Table 2.4DC Characteristics (2) (1/2)Conditions: $1.8 \vee \leq \text{VCC} = \text{VCC}_\text{USB} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \leq 2.7 \vee, 1.8 \vee \leq \text{AVCCO} < 2.7 \vee, \\ \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \vee, T_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Schmitt trigger input voltage	P16, P17, PB5 (5 V tolerant)		V _{IH}	VCC × 0.8	—	5.8	V	
	P14, P15, P21, P22, P25 to P35 to P37, PB0, PB1, PB3, PC0, PC2 to PC7 PD3, PE0 to PE4, PJ3, P30, P31 (other than RTCI RES#	PB7, 7,	1	VCC × 0.8	_	VCC + 0.3		
	P03, P05, P07, F	240 to P47		AVCC0 × 0.8	_	AVCC0 + 0.3		
	P30, P31 (RTCICn pin)	When VCC is supplied		VCC × 0.8	—	VCC + 0.3		
		When VBATT is supplied		VBATT × 0.8	—	VBATT + 0.3		
	P14 to P17, P21, P22, P25 to P35 to P37, PB0, PB1, PB3, PC0, PC2 to PC7 PD3, PE0 to PE4, PJ3, P30, P31 (other than RTCI RES#	PB5, PB7, 7,	V _{IL}	-0.3	_	VCC × 0.2		
	P03, P05, P07, P40 to P47			-0.3	_	AVCC0 × 0.2		
	P30, P31 (RTCICn pin)	When VCC is supplied		-0.3	_	VCC × 0.2]	
		When VBATT is supplied		-0.3	_	VBATT × 0.2		



Table 2.4DC Characteristics (2) (2/2)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_USB = \text{VCC}_RF = \text{AVCC}_RF \le 2.7 \text{ V}, 1.8 \text{ V} \le \text{AVCC0} < 2.7 \text{ V}, VSS = \text{AVSS0} = \text{VSS}_USB = \text{VSS}_RF = 0 \text{ V}, T_a = -40 \text{ to } +85^{\circ}\text{C}$

	ltem	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Schmitt trigger input voltage	P14 to P17, P21, P22, P25 to P27, P35 to P37, PB0, PB1, PB3, PB5, PB7, PC0, PC2 to PC7, PD3, PE0 to PE4, PJ3, P30, P31 (other than RTCICn pin), RES#	ΔV _T	VCC × 0.1	_		V	
	P03, P05, P07, P40 to P47		AVCC0 × 0.1				
Input level	MD	V _{IH}	VCC × 0.9		VCC + 0.3	V	
voltage (except for Schmitt	EXTAL (external clock input)		VCC × 0.8	_	VCC + 0.3		
trigger input	MD	V _{IL}	-0.3	_	VCC × 0.1		
pins)	EXTAL (external clock input)		-0.3		VCC × 0.2		

Table 2.5DC Characteristics (3)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Input leakage current RES#, MD, P35		I _{in}	—		1.0	μA	V _{in} = 0 V, VCC
Three-state leakage current (off-state)	6		—	—	1.0	μA	V _{in} = 0 V, 5.8 V
	Ports except for 5 V tolerant		_	_	0.2	μA	V _{in} = 0 V, VCC
Input capacitance All input pins (except for P35, USB0_DM, USB0_DP)		C _{in}	—	—	15	pF	$V_{in} = 0 mV,$ f = 1 MHz, T _a = 25°C
	P35, USB0_DM, USB0_DP	1	—	_	30		

Table 2.6DC Characteristics (4)

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

Item			Min.	Тур.	Max.	Unit	Test Conditions
Input pull-up resistor All ports (except for P35)		R _U	10	20	50	kΩ	V _{in} = 0 V



Table 2.7DC Characteristics (5)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

Item						Typ. *4	Max.	Unit	Test Conditions
Supply	High-speed	Normal	No peripheral	ICLK = 54 MHz	I _{CC}	6.5	_	mA	
current *1	operating mode	operating mode	operation*2	ICLK = 32 MHz		4.1	_		
				ICLK = 16 MHz		2.9	_		
				ICLK = 8 MHz		2.2	_		
				ICLK = 4 MHz		1.9	_		
			All peripheral	ICLK = 54 MHz*11		26.5	_		
			operation: Normal	ICLK = 32 MHz*3		21.0	_		
				ICLK = 16 MHz*3		11.8	_		
				ICLK = 8 MHz*3		6.6	_		
				ICLK = 4 MHz*3		4.2	—		
			All peripheral	ICLK = 54 MHz*11		_	53.3		
			operation: Max. Increase due to operation of the Trusted Secure IP No peripheral	ICLK = 32 MHz*3		_	40.8		
				PCLKB = 32 MHz		_	2		
		Sleep mode		ICLK = 54 MHz		3.5	_		
			operation*2	ICLK = 32 MHz		2.4	_		
				ICLK = 16 MHz		1.9	_		
				ICLK = 8 MHz		1.6	_		
				ICLK = 4 MHz		1.5	_		
			All peripheral operation: Normal	ICLK = 54 MHz*11		13.4	_		
				ICLK = 32 MHz*3		12.5			
				ICLK = 16 MHz*3		7.3	_		
				ICLK = 8 MHz*3		4.6	_		
				ICLK = 4 MHz*3		3.3	—		
		Deep sleep	No peripheral operation*2	ICLK = 54 MHz		2.3	—		
	mode	mode		ICLK = 32 MHz		1.5	—		
				ICLK = 16 MHz		1.3	—		
				ICLK = 8 MHz		1.2	—		
				ICLK = 4 MHz		1.1	—		
			All peripheral operation: Normal	ICLK = 54 MHz*11		10.6	—		
				ICLK = 32 MHz*3		9.9	—		
				ICLK = 16 MHz*3		5.9	—		
				ICLK = 8 MHz*3		3.8	—		
				ICLK = 4 MHz*3		2.7	—		
		Increase during I	BGO operation* ⁵			2.5	—		
	Middle-speed operating mode	Normal operating mode	No peripheral operation* ⁶	ICLK = 12 MHz	I _{CC}	2.7	_	mA	
	operating mode	operating mode	operation *	ICLK = 8 MHz		1.8	_		
				ICLK = 4 MHz		1.4	_		
				ICLK = 1 MHz		1.1	_		
			All peripheral operation: Normal* ⁷	ICLK = 12 MHz		9.6	—		
				ICLK = 8 MHz		6.2	—		
				ICLK = 4 MHz		3.8			
				ICLK = 1 MHz		2.3	—		L



		Ite	m		Symbol	Тур. *4	Max.	Unit	Test Conditions
Supply current	Middle-speed operating mode	Normal operating mode	All peripheral operation: Max.*7	ICLK = 12 MHz	I _{CC}	_	16.7	mA	
*1	Sleep mode No periphe	No peripheral				_			
			operation* ⁶	ICLK = 8 MHz		1.2	—		
				ICLK = 4 MHz		1.1	_		
				ICLK = 1 MHz		1.0	_		
			All peripheral	ICLK = 12 MHz		6.1	_		
			operation: Normal*7	ICLK = 8 MHz		4.4	—		
				ICLK = 4 MHz		3.0	—		
				ICLK = 1 MHz		2.0	—		
	Deep sleep No peripheral		ICLK = 12 MHz		1.6				
		mode	operation* ⁶	ICLK = 8 MHz		1.0	—		
				ICLK = 4 MHz		0.9	—		
			ICLK = 1 MHz		0.8	—			
			All peripheral operation: Normal* ⁷	ICLK = 12 MHz		5.1	—		
				ICLK = 8 MHz		3.7			
				ICLK = 4 MHz		2.6			
				ICLK = 1 MHz		1.8			
		Increase during E	3GO operation*5			2.5			
	Low-speed operating mode	Normal operating mode	No peripheral operation* ⁸	ICLK = 32 kHz	I _{CC}	5.2		μA	
		Sleep mode All periphera operation: N Sleep mode All periphera operation*8 All periphera operation: N	All peripheral operation: Normal *9, *10	ICLK = 32 kHz		22.3			
			All peripheral operation: Max.* ^{9, *10}	ICLK = 32 kHz			74.4		
			No peripheral operation* ⁸	ICLK = 32 kHz		3.0	_		
			All peripheral operation: Normal* ⁹	ICLK = 32 kHz		13.1	—		
			No peripheral operation* ⁸	ICLK = 32 kHz		2.4			
			All peripheral operation: Normal* ⁹	ICLK = 32 kHz		10.5			

Note 1. Supply current values do not include the output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

Note 2. Clock supply to the peripheral functions is stopped. This does not include BGO operation. The clock source is PLL. FCLK, and PCLK are set to divided by 64.

Note 3. Clocks are supplied to the peripheral functions. This does not include BGO operation. The clock source is PLL. FCLK, and PCLK are the same frequency as that of ICLK.

Note 4. Values when VCC is 3.3 V.

Note 5. This is the increase when data is programmed to or erased from the ROM or E2 DataFlash during program execution.

Note 6. Clock supply to the peripheral functions is stopped. The clock source is PLL when ICLK is 12 MHz and HOCO for other cases. FCLK, and PCLK are set to divided by 64.

Note 7. Clocks are supplied to the peripheral functions. The clock source is PLL when ICLK is 12 MHz and HOCO for other cases. FCLK, and PCLK are the same frequency of that of the ICLK.

Note 8. Clock supply to the peripheral functions is stopped. The clock source is the sub oscillation circuit. FCLK, and PCLK are set to divided by 64.

Note 9. Clocks are supplied to the peripheral functions. The clock source is the sub oscillation circuit. FCLK, and PCLK are the same frequency as that of ICLK.

Note 10. This is the value when the MSTPCRA.MSTPA17 (12-bit A/D converter module stop bit) is in the module stop state.

Note 11. Clocks are supplied to the peripheral functions. This does not include BGO operation. The clock source is PLL. FCLK, and PCLKB are set to divided by 2 and PCLKA and PCLKD are the same frequency as that of ICLK.



Figure 2.1 Volta

Voltage Dependency in High-Speed Operating Mode (Reference Data)











Table 2.8DC Characteristics (6)

Conditions: 1.8 V \leq VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \leq 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

Item			Symbol	Typ.* ³	Max.	Unit	Test Conditions
current*1 mode*2	Software standby	T _a = 25°C	I _{CC}	0.8	3.7	μA	
	T _a = 55°C		1.2	4.3			
		T _a = 85°C		3.5	18.6		
	Increment for IWD		0.4	_			
	Increment for LPT operation Increment for RTC operation*4			0.4			Use IWDT-Dedicated On-Chip Oscillator for clock source
				0.4	_		RCR3.RTCDV[2:0] set to low drive capacity
				1.2	_		RCR3.RTCDV[2:0] set to normal drive capacity

Note 1. Supply current values are with all output pins unloaded and all input pull-up MOSs in the off state.

Note 2. The IWDT, LVD, and CMPB are stopped.

Note 3. When VCC is 3.3 V.

Note 4. This increment includes the oscillation circuit.



Figure 2.4 Voltage Dependency in Software Standby Mode (Reference Data)



Figure 2.5 Temperature Dependency in Software Standby Mode (Reference Data)

Table 2.9DC Characteristics (7)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	ltem		Symbol	Тур.	Max.	Unit	Test Conditions
Supply	RTC operation	T _a = 25°C	I _{CC}	0.8	_	μA	VBATT = 2.0 V
current*1	when VCC is off	T _a = 55°C		0.9	—		RCR3.RTCDV[2:0] set to low drive capacity
		T _a = 85°C		1.0	—		
		T _a = 25°C		0.9	_		VBATT = 3.3 V
		T _a = 55°C		1.0	_		RCR3.RTCDV[2:0] set to low drive capacity
		T _a = 85°C		1.1	—		
		T _a = 25°C		1.5	—		VBATT = 2.0 V
		T _a = 55°C		1.8	_		RCR3.RTCDV[2:0] set to normal drive capacity
		T _a = 85°C		2.1	_		oupuoity
		T _a = 25°C		1.6	_		VBATT = 3.3 V
		T _a = 55°C	1	1.9	—		RCR3.RTCDV[2:0] set to normal drive capacity
		T _a = 85°C	1	2.2	—		

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.


Figure 2.6 Temperature Dependency of RTC Operation with VCC Off (Reference Data)

Table 2.10DC Characteristics (8)

```
Conditions: 1.8 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V
```

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Permissible total power consumption*1	Pd		—	350	mW	D-version product

Note 1. Total power dissipated by the entire chip (including output currents)



Table 2.11DC Characteristics (9)

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to $+85^{\circ}C$

	Item	Symbol	Min.	Typ.* ⁷	Max.	Unit	Test Conditions
Analog power	During A/D conversion (at high-speed conversion)	I _{AVCC}	_	0.7	1.7	mA	
supply current	During A/D conversion (in low-current mode)			0.6	1.0		
	During D/A conversion (per channel)*1			0.4	0.8		
	Waiting for A/D and D/A conversion (all units)			—	0.4	μA	
Reference	During A/D conversion (at high-speed conversion)	I _{REFH0}		25	150	μA	
power supply current	Waiting for A/D conversion (all units)			—	60	nA	
ourient	During D/A conversion (per channel)	I _{REFH}		50	100	μA	
	Waiting for D/A conversion (all units)			—	100	nA	
LVD1	—	I _{LVD}	_	0.15	_	μA	
Temperature sensor* ⁶	_	I _{TEMP}	—	75	—	μA	
Comparator B	Window mode	I _{CMP} *5	—	12.5	28.6	μA	
operating current* ⁶	Comparator high-speed mode (per channel)		_	3.2	16.2	μA	
Guirent	Comparator low-speed mode (per channel)		_	1.7	4.4	μA	
CTSU operating current	 When sleep mode Base clock frequency: 2MHz Pin capacitance: 50pF 	I _{CTSU}		150	_	μA	
USB operating current* ⁴	 During USB communication operation under the following settings and conditions Host controller operation is set to full-speed mode Bulk OUT transfer (64 bytes) × 1, bulk IN transfer (64 bytes) × 1 Connect peripheral devices via a 1-meter USB cable from the USB port. 	I _{USBH} *2		4.3 (VCC) 0.9 (VCC_USB)		mA	
	 During USB communication operation under the following settings and conditions Function controller operation is set to full-speed mode Bulk OUT transfer (64 bytes) × 1, bulk IN transfer (64 bytes) × 1 Connect the host device via a 1-meter USB cable from the USB port. 	I _{USBF} *2		3.6 (VCC) 1.1 (VCC_USB)		mA	
	 During suspended state under the following setting and conditions Function controller operation is set to full-speed mode (pull up the USB0_DP pin) Software standby mode Connect the host device via a 1-meter USB cable from the USB port. 	I _{SUSP} *3		0.35 (VCC) 170 (VCC_USB)		μA	

Note 1. The value of the D/A converter is the value of the power supply current including the reference current.

Note 2. Current consumed only by the USB module.

Note 3. Includes the current supplied from the pull-up resistor of the USB0_DP pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.

Note 4. Current consumed by the power supplies (VCC and VCC_USB).

Note 5. Current consumed only by the comparator B module.

Note 6. Current consumed by the power supply (VCC).

Note 7. When VCC = AVCC0 = VCC_USB = 3.3 V.



Table 2.12DC Characteristics (10)

Conditions: VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF = 3.3 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = +25^{\circ}C$

		Ty	/p.		
Item	Symbol	Transmit o	utput power	Unit	Test Conditions
		0 dBm	4 dBm		
BLE operating current	ldd_tx	4.3	8.7	mA	Transmit mode, 2Mbps
(when the DC-to-DC converter is selected)					Transmit mode, 1Mbps
selected		4.5	8.7		Transmit mode, 500kbps
					Transmit mode, 125kbps
	ldd_rx	3.0	3.5	mA	Receive mode, 2Mbps Prf = –67dBm
		3.0	3.4		Receive mode, 1Mbps Prf = –67dBm
		3.2	3.5		Receive mode, 500kbps Prf = –72dBm
		3.3	3.5		Receive mode, 125kbps Prf = –79dBm
	Idd_idle	0.5		mA	Idle mode
	ldd_slp	1.5		μA	Deep sleep mode
	ldd_down	0.1		μA	Power down mode
BLE operating current	ldd_tx	10.2	18.1	mA	Transmit mode, 2Mbps
(when the linear regulator is selected)					Transmit mode, 1Mbps
					Transmit mode, 500kbps
					Transmit mode, 125kbps
	ldd_rx	6	.9	mA	Receive mode, 2Mbps Prf = –67dBm
		6	.9		Receive mode, 1Mbps Prf = –67dBm
		6	.9		Receive mode, 500kbps Prf = –72dBm
		7	.1		Receive mode, 125kbps Prf = -79dBm
	Idd_idle	0	.7	mA	Idle mode
	ldd_slp	1	.5	μA	Deep sleep mode
	ldd_down	0	.1	μA	Power down mode

Table 2.13DC Characteristics (11)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

ltem	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
RAM standby voltage	V _{RAM}	1.8		_	V	

Table 2.14DC Characteristics (12)

Conditions: $0 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Power-on VCC rising gradient	At normal startup*1	SrVCC	0.02	-	20	ms/V	
	During fast startup time*2		0.02	_	2		
	Voltage monitoring 0 reset enabled at startup* ^{3, *4}		0.02		_		

Note 1. When OFS1.(FASTSTUP, LVDAS) bits are 11b.

Note 2. When OFS1.(FASTSTUP, LVDAS) bits are 01b.

Note 3. When OFS1.LVDAS bit is 0.

Note 4. Turn on the power supply voltage according to the normal startup rising gradient because the settings in the OFS1 register are not read in boot mode.

Table 2.15DC Characteristics (13)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

The ripple voltage must meet the allowable ripple frequency $f_{r (VCC)}$ within the range between the VCC upper limit and lower limit. When VCC change exceeds VCC ±10%, the allowable voltage change rising/falling gradient dt/dVCC must be met.

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Allowable ripple frequency	f _{r (VCC)}	—	_	10	kHz	Figure 2.7 $V_{r (VCC)} \le VCC \times 0.2$
		—	_	1	MHz	Figure 2.7 V _{r (VCC)} ≤ VCC × 0.08
		—	_	10	MHz	Figure 2.7 V _{r (VCC)} ≤ VCC × 0.06
Allowable voltage change rising/falling gradient	dt/dVCC	1.0	_	—	ms/V	When VCC change exceeds VCC ±10%



Figure 2.7 Ripple Waveform

Table 2.16DC Characteristics (14)

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

ltem	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Permissible error of VCL pin external capacitance	C _{VCL}	1.4	4.7	7.0	μF	

Note: The recommended capacitance is 4.7 µF. Variations in connected capacitors should be within the above range.



Table 2.17 Permissible Output Currents

Conditions: 1.8 V \leq VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \leq 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

	Item		Symbol	Max.	Unit
Permissible output low current	P03, P05, P07, P36, P37, F	P40 to P47	I _{OL}	4.0	mA
(average value per pin)	Ports other than above	Normal output mode		4.0	
		High-drive output mode	al output mode 4.0 drive output mode 8.0 al output mode 4.0 al output mode 4.0 drive output mode 8.0 drive output mode 8.0 Del P27, P30, P31, P35 to 40 C0, PC2 to PC7 40 A0 80 C0, PC2 to PC7 40 al output mode -4.0 drive output mode -4.0 al output mode -4.0 drive output mode -4.0 P27, P30, P31, P35 to SI _{OH}	8.0	
Permissible output low current	P03, P05, P07, P36, P37, F	P40 to P47		4.0	
(maximum value per pin)	Ports other than above	Normal output mode		4.0	
		High-drive output mode		8.0	
Permissible output low current	Total of P03, P05, P07, P40) to P47	ΣI_{OL}	40	
	Total of P14 to P17, P21, P P37, PJ3	22, P25 to P27, P30, P31, P35 to		40	
	Total of PB0, PB1, PB3, PB	5, PB7, PC0, PC2 to PC7		40	
	Total of PD3, PE0 to PE4			40	
	Total of all output pins		80		
Permissible output high current	P03, P05, P07, P36, P37, P	I _{ОН}	-4.0		
(average value per pin)	Ports other than above	Normal output mode		-4.0	
		High-drive output mode		-8.0	
average value per pin) Permissible output high current	P03, P05, P07, P36, P37, F	P40 to P47		-4.0	
(maximum value per pin)	Ports other than above	Normal output mode		-4.0	
		High-drive output mode		-8.0	
Permissible output high current	Total of P03, P05, P07, P40) to P47	Σl _{OH}	-40	
Permissible output high current (maximum value per pin) Permissible output high current	Total of P14 to P17, P21, P P37, PJ3	22, P25 to P27, P30, P31, P35 to		-40	
	Total of PB0, PB1, PB3, PB	5, PB7, PC0, PC2 to PC7]	-40	
	Total of PD3, PE0 to PE4		1	-40	1
	Total of all output pins]	-80	1

Note: Do not exceed the permissible total supply current.



Table 2.18 Output Values of Voltage (1)

Conditions: 1.8 V \leq VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \leq 2.7 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

	Item			Symbol	Min.	Max.	Unit	Test Conditions
Output low	All output ports*1	Normal output mode High-drive output mode		V _{OL}	—	0.8	V	I _{OL} = 0.5 mA
					—	0.8		I _{OL} = 1.0 mA
Output high	All output ports*1	Normal output mode	P03, P05, P07, P40 to P47	V _{OH}	AVCC0 - 0.5	_	V	I _{OH} = -0.5 mA
			Ports other than above		VCC - 0.5	—		
		High-drive outp	out mode	1	VCC - 0.5	_		I _{OH} = -1.0 mA

Note 1. This excludes the CLKOUT_RF pin.

Table 2.19Output Values of Voltage (2)

Conditions: $2.7 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

	lt	tem		Symbol	Min.	Max.	Unit	Test Conditions	
Output low	All output ports	Normal output	mode	V _{OL}	—	0.8	V	I _{OL} = 1.0 mA	
	(except for RIIC) *1	High-drive output mode			—	0.8		I _{OL} = 2.0 mA	
	RIIC pins	Standard mode mode)	e (Normal output		_	0.4		I _{OL} = 3.0 mA	
		Fast mode (High-drive output mode)			—	0.6		I _{OL} = 6.0 mA	
Output high	All output ports*1	Normal output mode	P03, P05, P07, P40 to P47	V _{OH}	AVCC0 - 0.8	_	V	I _{OH} = -1.0 mA	
			Ports other than above		VCC - 0.8	_			
		High-drive outp	out mode	1	VCC - 0.8	_		I _{OH} = -2.0 mA	

Note 1. This excludes the CLKOUT_RF pin.

Table 2.20Output Values of Voltage (3)

Conditions: $3.0V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0V, Ta = -40 to +85°C

	Item	Symbol	Min.	Max.	Unit	Test Conditions
Output low	CLKOUT_RF	V _{OL}	_	0.3	V	I _{OL} = 0.5 mA
Output high	CLKOUT_RF	V _{OH}	VCC_RF - 0.3	—	V	I _{OH} = -0.5 mA

2.2.1 Normal I/O Pin Output Characteristics (1)

Figure 2.8 to Figure 2.11 show the characteristics when normal output is selected by the drive capacity control register.



Figure 2.8 V_{OH}/V_{OL} and I_{OH}/I_{OL} Voltage Characteristics at $T_a = 25^{\circ}$ C When Normal Output is Selected (Reference Data)



Figure 2.9 V_{OH}/V_{OL} and I_{OH}/I_{OL} Temperature Characteristics at VCC = 1.8 V When Normal Output is Selected (Reference Data)



Figure 2.10 V_{OH}/V_{OL} and I_{OH}/I_{OL} Temperature Characteristics at VCC = 2.7 V When Normal Output is Selected (Reference Data)



Figure 2.11 V_{OH}/V_{OL} and I_{OH}/I_{OL} Temperature Characteristics at VCC = 3.3 V When Normal Output is Selected (Reference Data)

2.2.2 Normal I/O Pin Output Characteristics (2)

Figure 2.12 to Figure 2.15 show the characteristics when high-drive output is selected by the drive capacity control register.







Figure 2.13 V_{OH}/V_{OL} and I_{OH}/I_{OL} Temperature Characteristics at VCC = 1.8 V When High-Drive Output is Selected (Reference Data)



Figure 2.14 V_{OH}/V_{OL} and I_{OH}/I_{OL} Temperature Characteristics at VCC = 2.7 V When High-Drive Output is Selected (Reference Data)



Figure 2.15 V_{OH}/V_{OL} and I_{OH}/I_{OL} Temperature Characteristics at VCC = 3.3 V When High-Drive Output is Selected (Reference Data)

2.2.3 Normal I/O Pin Output Characteristics (3)

Figure 2.16 to Figure 2.18 show the characteristics of the RIIC output pin.







Figure 2.17 V_{OL} and I_{OL} Temperature Characteristics of RIIC Output Pin at VCC = 2.7 V (Reference Data)



Figure 2.18 V_{OL} and I_{OL} Temperature Characteristics of RIIC Output Pin at VCC = 3.3 V (Reference Data)



2.3 AC Characteristics

2.3.1 Clock Timing

Table 2.21 Operating Frequency Value (High-Speed Operating Mode)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC0} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = \text{VSS}_{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

			VCC						
	Item	Symbol	1.8 V ≤ VCC < 2.4 V	2.4 V ≤ VCC < 2.7 V	2.7 V ≤ VCC ≤ 3.6 V	When USB is in Use*3	Unit		
Maximum	System clock (ICLK)	f _{max}	8	16	54	54	MHz		
operating frequency* ⁴	FlashIF clock (FCLK)*1, *2		8	16	32	32			
inequency ·	Peripheral module clock (PCLKA)		8	16	54	54			
	Peripheral module clock (PCLKB)		8	16	32	32			
	Peripheral module clock (PCLKD)		8	32	54	54			
	USB clock (UCLK)	f _{usb}	—	—	—	48			

Note 1. The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When FCLK is in use at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 2. The frequency accuracy of FCLK must be within $\pm 3.5\%$.

Note 3. The VCC_USB range is 3.0 to 3.6 V when the USB clock is in use.

Note 4. The maximum operating frequency listed above does not include errors of the external oscillator and internal oscillator. For details on the range for the guaranteed operation, see Table 2.24, Clock Timing.

Table 2.22 Operating Frequency Value (Middle-Speed Operating Mode)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

				V	00		
	Item			2.4 V ≤ VCC < 2.7 V	2.7 V ≤ VCC ≤ 3.6 V	When USB is in Use*3	Unit
Maximum	System clock (ICLK)	f _{max}	8	12	12	12	MHz
operating frequency* ⁴	FlashIF clock (FCLK)*1, *2		8	12	12	12	
nequency	Peripheral module clock (PCLKA)		8	12	12	12	
	Peripheral module clock (PCLKB)		8	12	12	12	
	Peripheral module clock (PCLKD)		8	12	12	12	
	USB clock (UCLK)	f _{usb}	—	—	—	48	

Note 1. The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 2. The frequency accuracy of FCLK must be within $\pm 3.5\%$.

Note 3. The VCC_USB range is 3.0 to 3.6 V when the USB clock is in use.

Note 4. The maximum operating frequency listed above does not include errors of the external oscillator and internal oscillator. For details on the range for the guaranteed operation, see Table 2.24, Clock Timing.



Table 2.23 **Operating Frequency Value (Low-Speed Operating Mode)**

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

				VCC				
	Item	Symbol	1.8 V ≤ VCC < 2.4 V	2.4 V ≤ VCC < 2.7 V	2.7 V ≤ VCC ≤ 3.6 V	Unit		
Maximum	System clock (ICLK)	f _{max}		32.768		kHz		
operating frequency* ³	FlashIF clock (FCLK)*1			32.768				
noquonoy	Peripheral module clock (PCLKA)			32.768				
	Peripheral module clock (PCLKB)			32.768				
	Peripheral module clock (PCLKD)*2				1			

Note 1. Programming and erasing the flash memory is impossible.

Note 2. The A/D converter cannot be used. Note 3. The maximum operating frequency listed above does not include errors of the external oscillator. For details on the range for the guaranteed operation, see Table 2.24, Clock Timing.



Table 2.24Clock Timing

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0= VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
EXTAL external clock input cycle	time	t _{Xcyc}	50	—		ns	Figure 2.19
EXTAL external clock input high	pulse width	t _{XH}	20	—		ns	-
EXTAL external clock input low p	ulse width	t _{XL}	20	—		ns	-
EXTAL external clock rise time		t _{Xr}	_	—	5	ns	-
EXTAL external clock fall time		t _{Xf}	_	—	5	ns	_
EXTAL external clock input wait	time*1	t _{XWT}	0.5	—		μs	
Main clock oscillator oscillation	2.4 ≤ VCC ≤ 3.6	f _{MAIN}	1	—	20	MHz	-
frequency*2	1.8 ≤ VCC < 2.4	-	1	_	8		
Main clock oscillation stabilizatio	n time (crystal)*2	t _{MAINOSC}	_	3	—	ms	Figure 2.20
Main clock oscillation stabilizatio resonator)*2	t _{MAINOSC}		50	_	μs		
LOCO clock oscillation frequency	/	f _{LOCO}	3.44	4.0	4.56	MHz	
LOCO clock oscillation stabilizati	on time	t _{LOCO}	_	—	0.5	μs	Figure 2.21
IWDT-dedicated clock oscillation	frequency	f _{ILOCO}	12.75	15	17.25	kHz	
IWDT-dedicated clock oscillation	IWDT-dedicated clock oscillation stabilization time			—	50	μs	Figure 2.22
Bluetooth-dedicated clock oscilla	tion frequency	f _{BLECK}	_	32		MHz	
Bluetooth-dedicated low-speed coscillation frequency	n-chip oscillator	f _{BLELOCO}	—	32.768	—	kHz	
HOCO clock oscillation frequence	у	f _{HOCO}	31.36	32	32.64	MHz	$T_a = 0$ to +85°C
		(32 MHz)	31.04	32	32.96		$T_a = -40 \text{ to } +85^{\circ}\text{C}$
		f _{HOCO}	52.96	54	55.08	MHz	$T_a = 0$ to +85°C
		(54 MHz)	52.38	54	55.62		$T_a = -40 \text{ to } +85^{\circ}\text{C}$
HOCO clock oscillation stabilizat	ion time	t _{HOCO}	_	—	30	μs	Figure 2.24
PLL input frequency*3		f _{PLLIN}	4	—	12.5	MHz	
PLL circuit oscillation frequency*	3	f _{PLL}	24	—	54	MHz	
PLL clock oscillation stabilization	time	t _{PLL}	_	—	50	μs	Figure 2.25
PLL free-running oscillation frequ	iency	f _{PLLFR}	_	8		MHz	
USBPLL input frequency*5	f _{PLLIN}	—	4, 6, 8, 12	_	MHz		
USBPLL circuit oscillation freque	f _{PLL}	—	48* ⁶	_	MHz		
USBPLL clock oscillation stabiliz	t _{PLL}	—	—	50	μs	Figure 2.25	
Sub-clock oscillator oscillation fre	equency*7	f _{SUB}	—	32.768	_	kHz	
Sub-clock oscillation stabilization	ı time*4	t _{SUBOSC}	_	0.5		s	Figure 2.26

Note 1. Time until the clock can be used after the main clock oscillator stop bit (MOSCCR.MOSTP) is set to 0 (operating).

Note 2. Reference values when an 8-MHz resonator is used.

When specifying the main clock oscillator stabilization time, set the MOSCWTCR register with a stabilization time value that is equal to or greater than the resonator-manufacturer-recommended value.

After the MOSCCR.MOSTP bit is changed to enable the main clock oscillator, confirm that the OSCOVFSR.MOOVF flag has become 1, and then start using the main clock.

Note 3. The VCC range should be 2.4 to 3.6 V when the PLL is used.

Note 4. Reference values when a 32.768-kHz resonator is used.

After the setting of the SOSCCR.SOSTP bit or RCR3.RTCEN bit is changed to operate the sub-clock oscillator, only start using the sub-clock after the sub-clock oscillation stabilization wait time that is equal to or greater than the oscillator-manufacturer-recommended value has elapsed.

Note 5. The VCC range should be 3.0 to 3.6 V when the USBPLL is used.

Note 6. The oscillation frequency can be set to 48 MHz only.

Note 7. Only 32.768 kHz can be used.









Figure 2.20 Main Clock Oscillation Start Timing



Figure 2.21 LOCO Clock Oscillation Start Timing



Figure 2.22 IWDT-Dedicated Clock Oscillation Start Timing









Figure 2.24 HOCO Clock Oscillation Start Timing (Oscillation is Started by Setting HOCOCR.HCSTP Bit)



Figure 2.25 PLL Clock Oscillation Start Timing (PLL is Operated after Main Clock Oscillation Has Been Stabled)



Figure 2.26 Sub-Clock Oscillation Start Timing



2.3.2 Reset Timing

Table 2.25 Reset Timing

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
RES# pulse width	At power-on	t _{RESWP}	3	—	_	ms	Figure 2.27
	Other than above	t _{RESW}	30			μs	Figure 2.28
Wait time after RES#	At normal startup*1	t _{RESWT}		8.5		ms	Figure 2.27
cancellation (at power-on)	During fast startup time*2	t _{RESWT}		560	_	μs	
Wait time after RES# c (during powered-on sta	t _{RESWT}	—	120	—	μs	Figure 2.28	
Independent watchdog	timer reset period	t _{RESWIW}	_	1	_	IWDT clock cycle	Figure 2.29
Watchdog timer reset	period	t _{RESWWW}		4	—	PCLKB cycle	
Software reset period		t _{RESWSW}		1		ICLK cycle	
Wait time after indeper	t _{RESWT2}		300		μs		
Wait time after watchd	Wait time after watchdog timer reset cancellation*4			300	—	μs]
Wait time after softwar	t _{RESWT2}		170		μs]	

Note 1. When OFS1.(LVDAS, FASTSTUP) bits are 11b.

Note 2. When OFS1.(LVDAS, FASTSTUP) bits are a value other than 11b.

Note 3. When IWDTCR.CKS[3:0] bits are 0000b.

Note 4. When WDTCR.CKS[3:0] bits are 0001b.



Figure 2.27 Reset Input Timing at Power-On







Figure 2.29 Reset Input Timing (2)



2.3.3 Timing of Recovery from Low Power Consumption Modes

Table 2.26 Timing of Recovery from Low Power Consumption Modes (1)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item				Min.	Тур.	Max.	Unit	Test Conditions
Recovery time from software standby mode*1	High-speed mode	Crystal connected to main clock oscillator	Main clock oscillator operating* ²	t _{SBYMC}	—	2	3	ms	Figure 2.30
		External clock input to main clock oscillator	Main clock oscillator operating* ³	SDIEA			50	μs	
		Sub-clock oscillator o	t _{SBYSC}		650	800	μs		
		HOCO clock oscillato	HOCO clock oscillator operating		—	40	55	μs	
		LOCO clock oscillato	r operating	t _{SBYLO}		40	55	μs	

Note 1. The recovery time varies depending on the state of each oscillator when the WAIT instruction is executed. When multiple oscillators are operating, the recovery time varies depending on the operating state of the oscillators that are not selected as the system clock source. The above table applies when only the corresponding clock is operating.

Note 2. When the frequency of the crystal is 20 MHz. When the main clock oscillator wait control register (MOSCWTCR) is set to 04h.

Table 2.27 Timing of Recovery from Low Power Consumption Modes (2)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

		Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
	Middle-speed mode	Crystal connected to main clock oscillator	Main clock oscillator operating* ²	t _{SBYMC}	_	2	3	ms	Figure 2.30
			Main clock oscillator and PLL circuit operating* ³	t _{SBYPC}	_	2	3	ms	
		to main clock c oscillator N a	Main clock oscillator operating*4	t _{SBYEX}	_	3	4	μs	
			Main clock oscillator and PLL circuit operating ^{*5}	t _{SBYPE}	_	65	85	μs	
		Sub-clock oscillator o	perating	t _{SBYSC}	_	600	750	μs	
		HOCO clock oscillato	r operating* ⁶	t _{SBYHO}		40	50	μs	
	-	LOCO clock oscillato	r operating	t _{SBYLO}	_	5	7	μs	

Note 1. The recovery time varies depending on the state of each oscillator when the WAIT instruction is executed. When multiple oscillators are operating, the recovery time varies depending on the operating state of the oscillators that are not selected as the system clock source. The above table applies when only the corresponding clock is operating.
 Note 2. When the frequency of the crystal is 12 MHz.

When the main clock oscillator wait control register (MOSCWTCR) is set to 04h.

Note 3. When the frequency of PLL is 12 MHz.

When the main clock oscillator wait control register (MOSCWTCR) is set to 04h.

Note 4. When the frequency of the external clock is 12 MHz.

When the main clock oscillator wait control register (MOSCWTCR) is set to 00h.

Note 5. When the frequency of PLL is 12 MHz.

When the main clock oscillator wait control register (MOSCWTCR) is set to 00h.

Note 6. This is the case when HOCO is selected as the system clock and its frequency division is set to be 8 MHz.



Note 3. When the frequency of the external clock is 20 MHz. When the main clock oscillator wait control register (MOSCWTCR) is set to 00h.

Table 2.28 Timing of Recovery from Low Power Consumption Modes (3)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC0} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = \text{VSS}_{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

Item			Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Recovery time from software standby mode* ¹	Low-speed mode	Sub-clock oscillator operating	t _{SBYSC}		600	750	μs	Figure 2.30

Note 1. The sub-clock continues oscillating in software standby mode during low-speed mode.



Figure 2.30 Software Standby Mode Recovery Timing

Table 2.29 Timing of Recovery from Low Power Consumption Modes (4)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Recovery time from deep	High-speed mode*2	t _{DSLP}	—	2	3.5	μs	Figure 2.31
sleep mode*1	Middle-speed mode*3	t _{DSLP}	—	3	4	μs	
	Low-speed mode*4	t _{DSLP}	—	400	500	μs	

Note 1. Oscillators continue oscillating in deep sleep mode.

Note 2. When the frequency of the system clock is 32 MHz.

Note 3. When the frequency of the system clock is 12 MHz.

Note 4. When the frequency of the system clock is 32 kHz.







Table 2.30 Operating Mode Transition Time

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = \text{VSS}_{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

Mode before Transition	Mode after Transition		Tra	Unit		
Mode before transition		ICLK Frequency	Min.	Тур.	Max.	Unit
High-speed operating mode	Middle-speed operating modes	8 MHz	_	10	—	μs
Middle-speed operating modes	High-speed operating mode	8 MHz	—	37.5	—	μs
Low-speed operating mode	Middle-speed operating mode, high-speed operating mode	32.768 kHz	—	215	—	μs
Middle-speed operating mode, high-speed operating mode	Low-speed operating mode	32.768 kHz	_	185	_	μs

Note: Values when the frequencies of PCLKA, PCLKB, PCLKD, and FCLK, are not divided.



2.3.4 Control Signal Timing

Table 2.31Control Signal Timing

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to $+85^{\circ}C$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Cond	itions
NMI pulse width	t _{NMIW}	200	—	—	ns	NMI digital filter is disabled	t _{Pcyc} × 2 ≤ 200 ns
		t _{Pcyc} × 2*1		_		(NMIFLTE.NFLTEN = 0)	t _{Pcyc} × 2 > 200 ns
		200	—	_		NMI digital filter is enabled	t _{NMICK} × 3 ≤ 200 ns
		t _{NMICK} × 3.5* ²	—	—		(NMIFLTE.NFLTEN = 1)	t _{NMICK} × 3 > 200 ns
IRQ pulse width	t _{IRQW}	200	_	_	ns	IRQ digital filter is disabled	t _{Pcyc} × 2 ≤ 200 ns
		t _{Pcyc} × 2* ¹		_		(IRQFLTE0.FLTENi = 0)	t _{Pcyc} × 2 > 200 ns
		200	—	—	1	IRQ digital filter is enabled	t _{IRQCK} × 3 ≤ 200 ns
		t _{IRQCK} × 3.5* ³		_		(IRQFLTE0.FLTENi = 1)	t _{IRQCK} × 3 > 200 ns

Note: 200 ns minimum in software standby mode.

Note 1. t_{Pcyc} indicates the cycle of PCLKB.

Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.

Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock (i = 0 to 7).



Figure 2.32 NMI Interrupt Input Timing







2.3.5 Timing of On-Chip Peripheral Modules

2.3.5.1 Timing of I/O Ports

Table 2.32Timing of I/O Ports

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC0} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = \text{VSS}_{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item	Symbol	Min.	Max.	Unit *1	Test Conditions
I/O ports	Input data pulse width	t _{PRW}	1.5	—	t _{Pcyc}	Figure 2.34

Note 1. t_{Pcyc}: PCLK cycle







2.3.5.2 Timing of MTU/TPU

Table 2.33Timing of MTU/TPU

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

	Item	Symbol	Min.	Max.	Unit *1	Test Conditions	
MTU/TPU	Input capture input pulse width	Single-edge setting	t _{TICW}	1.5	-	t _{Pcyc}	Figure 2.35
		Both-edge setting		2.5	_		
	Timer clock pulse width Single-edg		t _{TCKWH} ,	1.5	—	t _{Pcyc}	Figure 2.36
Both-e		Both-edge setting	t _{TCKWL}	2.5	—		
		Phase counting mode		2.5	—		

Note 1. t_{Pcyc}: PCLK cycle



Figure 2.35 MTU Input/Output Timing



Figure 2.36 MTU Clock Input Timing



2.3.5.3 Timing of POE

Table 2.34Timing of POE

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to $+85^{\circ}C$

Item		Symbol	Min.	Max.	Unit *1	Test Conditions
POE	POE# input pulse width	t _{POEW}	1.5	-	t _{Pcyc}	Figure 2.37

Note 1. t_{Pcyc}: PCLK cycle





2.3.5.4 Timing of TMR

Table 2.35 Timing of TMR

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

Item		Symbol	Min.	Max.	Unit *1	Test Conditions	
TMR	Timer clock pulse width	Single-edge setting	t _{TMCWH} ,	1.5	_	t _{Pcyc}	Figure 2.38
		Both-edge setting	t _{TMCWL}	2.5			

Note 1. t_{Pcyc}: PCLK cycle



Figure 2.38 TMR Clock Input Timing



2.3.5.5 Timing of SCI

Table 2.36 Timing of SCI

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item			Symbol	Min.	Max.	Unit *1	Test Conditions
SCI	Input clock cycle time	Input clock cycle time		t _{Scyc}	4	—	t _{Pcyc}	Figure 2.39
					6	—		
	Input clock pulse width	Input clock pulse width			0.4	0.6	t _{Scyc}	
	Input clock rise time	Input clock rise time			—	20	ns	
	Input clock fall time	Input clock fall time			—	20	ns	
	Output clock cycle time	Output clock cycle time		t _{Scyc}	16	—	t _{Pcyc}	Figure 2.40
			Clock synchronous		4	—		
	Output clock pulse width	Output clock pulse width			0.4	0.6	t _{Scyc}	-
	Output clock rise time	Output clock rise time			—	20	ns	
	Output clock fall time	Output clock fall time			—	20	ns	
	Transmit data delay time (master)	Clock synchro	nous	t _{TXD}	—	40	ns	
	Transmit data delay time	Clock	2.7 V or above			65	ns	
	(slave)	synchronous	1.8 V or above		_	100	ns	
	Receive data setup time	Clock	2.7 V or above	t _{RXS}	65	—	ns	-
	(master)	synchronous	1.8 V or above		90	—	ns	
	Receive data setup time (slave)	Clock synchro	nous	1	40	—	ns	1
	Receive data hold time	Clock synchro	nous	t _{RXH}	40	—	ns	

Note 1. t_{Pcyc}: PCLK cycle



Figure 2.39 SCK Clock Input Timing







Table 2.37Timing of Simple I²C

Conditions: $2.7 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC0} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = \text{VSS}_{RF} = 0 \text{ V}, \text{ fPCLKB} \le 32 \text{ MHz}, \text{ T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

	ltem	Symbol	Min.*1	Max.	Unit	Test Conditions	
Simple I ² C (Standard mode)	SSDA rise time	t _{Sr}	—	1000	ns	Figure 2.41	
	SSDA fall time	t _{Sf}	_	300	ns		
	SSDA spike pulse removal time	t _{SP}	0	4 × t _{Pcyc}	ns		
	Data setup time	t _{SDAS}	250	—	ns		
	Data hold time	t _{SDAH}	0	—	ns		
	SSCL, SSDA capacitive load	Cb	—	400	pF		
Simple I ² C	SSDA rise time	t _{Sr}	—	300	ns	Figure 2.41	
(Fast mode)	SSDA fall time	t _{Sf}	—	300	ns		
	SSDA spike pulse removal time	t _{SP}	0	4 × t _{Pcyc}	ns	-	
	Data setup time	t _{SDAS}	100	—	ns		
	Data hold time	t _{SDAH}	0	—	ns		
	SSCL, SSDA capacitive load	Cb	—	400	pF		

Note: t_{Pcyc}: PCLK cycle

Note 1. C_b is the total capacitance of the bus lines.





Figure 2.41 RIIC Bus Interface Input/Output Timing and Simple I²C Bus Interface Input/Output Timing

Table 2.38Timing of Simple SPI

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item		Symbol	Min.	Max.	Unit* ¹	Test Conditions
Simple	SCK clock cycle output (master)	SCK clock cycle output (master)			65536	t _{Pcyc}	Figure 2.42
SPI	SCK clock cycle input (slave)		6	65536	t _{Pcyc}		
	SCK clock high pulse width	t _{SPCKWH}	0.4	0.6	t _{SPcyc}		
	SCK clock low pulse width	t _{SPCKWL}	0.4	0.6	t _{SPcyc}		
	SCK clock rise/fall time	t _{SPCKr} , t _{SPCKf}	_	20	ns		
	Data input setup time (master)	2.7 V or above	t _{SU}	65	_	ns	Figure 2.43, Figure 2.44
		1.8 V or above		95			
	Data input setup time (slave)		40			-	
	Data input hold time	t _H	40		ns		
	SSL input setup time	t _{LEAD}	3		t _{SPcyc}		
	SSL input hold time	t _{LAG}	3		t _{SPcyc}		
	Data output delay time (master)	t _{OD}	_	40	ns		
	Data output delay time (slave)	2.7 V or above		_	65	1	
		1.8 V or above		—	100		
	Data output hold time (master)	2.7 V or above	t _{OH}	-10	_	ns	
		1.8 V or above		-20	_		
	Data output hold time (slave)		-10	_			
	Data rise/fall time	t _{Dr} , t _{Df}	_	20	ns		
	SSL input rise/fall time	t _{SSLr} , t _{SSLf}	—	20	ns	1	
	Slave access time	t _{SA}	—	6	t _{Pcyc}	Figure 2.45	
	Slave output release time	t _{REL}	—	6	t _{Pcyc}	Figure 2.46	

Note 1. t_{Pcyc}: PCLK cycle





Figure 2.42 RSPI Clock Timing and Simple SPI Clock Timing











Figure 2.45 RSPI Timing (Slave, CPHA = 0) and Simple SPI Clock Timing (Slave, CKPH = 1)



Figure 2.46 RSPI Timing (Slave, CPHA = 1) and Simple SPI Clock Timing (Slave, CKPH = 0)



Timing of RIIC 2.3.5.6

Table 2.39 **Timing of RIIC**

Conditions: 2.7 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, fPCLKB \leq 32 MHz, $\overline{T}_a = -40$ to +85°C

	Item	Symbol	Min.*1, *2	Max.	Unit	Test Conditions	
RIIC	SCL cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 1300	_	ns	Figure 2.47	
(Standard mode, SMBus)	SCL high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	_	ns		
	SCL low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	_	ns		
	SCL, SDA rise time		—	1000	ns		
	SCL, SDA fall time		—	300	ns		
	SCL, SDA spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns		
	SDA bus free time	t _{BUF}	3 (6) × t _{IICcyc} + 300	_	ns		
	START condition hold time	t _{STAH}	t _{IICcyc} + 300	_	ns		
	Repeated START condition setup time	t _{STAS}	1000	_	ns	-	
	STOP condition setup time	t _{STOS}	1000	_	ns		
	Data setup time	t _{SDAS}	t _{IICcyc} + 50	_	ns		
	Data hold time	t _{SDAH}	0	_	ns		
	SCL, SDA capacitive load	Cb	—	400	pF		
RIIC	SCL cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 600	_	ns	Figure 2.47	
(Fast mode)	SCL high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	_	ns		
	SCL low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	_	ns	_	
	SCL, SDA rise time	t _{Sr}	—	300	ns		
	SCL, SDA fall time	t _{Sf}	—	300	ns		
	SCL, SDA spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	1	
	SDA bus free time	t _{BUF}	3 (6) × t _{IICcyc} + 300	_	ns		
	START condition hold time	t _{STAH}	t _{IICcyc} + 300	_	ns		
	Repeated START condition setup time	t _{STAS}	300	_	ns		
	STOP condition setup time	t _{STOS}	300	_	ns		
	Data setup time	t _{SDAS}	t _{IICcyc} + 50	_	ns	,	
	Data hold time	t _{SDAH}	0	—	ns		
	SCL, SDA capacitive load	Cb	_	400	pF	1	

Note: t_{IICcyc} : RIIC internal reference clock (IIC ϕ) cycle Note 1. The value in parentheses is used when the ICMR3.NF[1:0] bits are set to 11b while a digital filter is enabled with the ICFER.NFE bit = 1.

Note 2. C_b is the total capacitance of the bus lines.





Figure 2.47 RIIC Bus Interface Input/Output Timing and Simple I²C Bus Interface Input/Output Timing



2.3.5.7 Timing of RSPI

Table 2.40Timing of RSPI

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V},$ $T_a = -40 \text{ to } +85^{\circ}\text{C}, \text{ C} = 30 \text{ pF}, \text{ when high-drive output is selected by the drive capacity control register}$

	lte	m	Symbol	Min.	Max.	Unit	Test Conditions
RSPCK clock	Master		t _{SPcyc}	2	4096	t _{Pcyc} *1	Figure 2.48
cycle	Slave			8	4096		
RSPCK clock high pulse widt	Master th		t _{SPCKWH}	(t _{SPcyc} – t _{SPCKr} – t _{SPCKf})/2 – 3	—	ns	
	Slave			(t _{SPcyc} – t _{SPCKr} – t _{SPCKf})/2	_		
RSPCK clock low pulse width	Master		t _{SPCKWL}	$(t_{SPcyc} - t_{SPCKr} - t_{SPCKf})/2 - 3$		ns	
	Slave			(t _{SPcyc} – t _{SPCKr} – t _{SPCKf})/2			
RSPCK clock	Output	2.7 V or above	t _{SPCKr} ,	—	10	ns	
rise/fall time		1.8 V or above	t _{SPCKf}	—	15		
	Input			_	1	μs	
Data input setu	p Master	2.7 V or above	t _{SU}	10	—	ns	Figure 2.49
time		1.8 V or above		30	_		to Figure 2.52
	Slave			25 – t _{Pcyc}	—		Figure 2.52
Data input holo time	Master	RSPCK set to a division ratio other than PCLKB divided by 2	t _H	t _{Pcyc}	_	ns	
		RSPCK set to PCLKB divided by 2	t _{HF}	0			
	Slave		t _H	20 + 2 × t _{Pcyc}	_		
SSL setup time	e Master		t _{LEAD}	$-30 + N^{*2} \times t_{SPcyc}$	_	ns	
	Slave			2	_	t _{Pcyc}	
SSL hold time	Master		t _{LAG}	$-30 + N^{*3} \times t_{SPcyc}$	—	ns	
	Slave			2	—	t _{Pcyc}	
Data output	Master	2.7 V or above	t _{OD}	—	14	ns	
delay time		1.8 V or above		—	30		
	Slave	2.7 V or above		_	3 × t _{Pcyc} + 65		
		1.8 V or above		—	3 × t _{Pcyc} +105		
Data output hol	d Master		t _{OH}	0	_	ns	
time	Slave			0	_		
Successive transmission	Master		t _{TD}	t_{SPcyc} + 2 × t_{Pcyc}	8 × t _{SPcyc} + 2 × t _{Pcyc}	ns	
delay time	Slave			4 × t _{Pcyc}	_		
MOSI and MIS	O Output	2.7 V or above	t _{Dr} , t _{Df}	—	10	ns	
rise/fall time		1.8 V or above		—	15		
	Input			—	1	μs	
SSL rise/fall	Output	2.7 V or above	t _{SSLr} ,	—	10	ns	1
time		1.8 V or above	t _{SSLf}	—	15	ns	
	Input			—	1	μs	1
Slave access t	ime	2.7 V or above	t _{SA}	_	6	t _{Pcyc}	Figure 2.51,
		1.8 V or above		_	7		Figure 2.52
Slave output release			4		F	4	1
Slave output re time	elease	2.7 V or above	t _{REL}	_	5	t _{Pcyc}	



Note 1.

Note 2.

t_{Pcyc}: PCLK cycle N: An integer from 1 to 8 that can be set by the RSPI clock delay register (SPCKD) N: An integer from 1 to 8 that can be set by the RSPI slave select negation delay register (SSLND) Note 3.














Figure 2.51 RSPI Timing (Slave, CPHA = 0) and Simple SPI Clock Timing (Slave, CKPH = 1)



Figure 2.52 RSPI Timing (Slave, CPHA = 1) and Simple SPI Clock Timing (Slave, CKPH = 0)



2.3.5.8 Timing of SSI

Table 2.41 Timing of SSI

Conditions: 1.8 V \leq VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \leq 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, fPCLKB \leq 32 MHz, T_a = -40 to +85°C

	Item		Symbol	Min.	Max.	Unit	Test Conditions
SSI	AUDIO_MCLK input	2.7 V or above	t _{AUDIO}	1	25	MHz	
	frequency	1.8 V or above		1	4		
	Output clock cycle	cycle		250	_	ns	Figure 2.53
	Input clock cycle		t _i	250	_	ns	
	Clock high level		t _{HC}	0.4	0.6	to, ti	
Clock low level			t _{LC}	0.4	0.6	to, ti	
	Clock rise time		t _{RC}	_	20	ns	
	Data delay time	2.7 V or above	t _{DTR}	_	65	ns	Figure 2.54
		1.8 V or above		_	105		Figure 2.55
	Setup time	2.7 V or above	t _{SR}	65	_	ns	
		1.8 V or above		90	_		
	Hold time		t _{HTR}	40	-	ns	1
	WS changing edge SSID	ATA output delay	t _{DTRW}	_	105	ns	Figure 2.56







Figure 2.54 SSI Transmission/Reception Timing (SSICR.SCKP = 0)



Figure 2.55 SSI Transmission/Reception Timing (SSICR.SCKP = 1)



Figure 2.56 SSIDATA Output Delay After SSIWSn Changing Edge



2.3.5.9 Timing of SDHI

Table 2.42 Timing of SDHI

Conditions: 2.7 V \leq VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \leq 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, fPCLKB \leq 32 MHz, T_a = -40 to +85°C,

when high-drive output is selected by the drive capacity control register

		Symbol	Min.	Max.	Unit	Test Conditions
SDHI	SDHI_CLK pin output cycle time	t _{PP(SD)}	62.5	—	ns	Figure 2.57
	SDHI_CLK pin output high pulse width	t _{WH(SD)}	18.25	—	ns	
	SDHI_CLK pin output low pulse width	t _{WL(SD)}	18.25	—	ns	
	SDHI_CLK pin output rise time	t _{TLH(SD)}	_	10	ns	
	SDHI_CLK pin output fall time	t _{THL(SD)}	_	10	ns	
	Output data delay time (data transfer mode) for SDHI_CMD and SDHI_D0 to SDHI_D3 pins	t _{ODLY(SD)}	-18.25	18.25	ns	
	Input data setup time for SDHI_CMD and SDHI_D0 to SDHI_D3 pins	t _{ISU(SD)}	9.25	—	ns	
	Input data hold time for SDHI_CMD and SDHI_D0 to SDHI_D3 pins	t _{IH(SD)}	8.3	—	ns	







2.3.5.10 Timing of A/D Converter Trigger

Table 2.43 Timing of A/D Converter Trigger

Conditions: 1.8 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

Item		Symbol	Min.	Max.	Unit *1	Test Conditions
A/D converter	Trigger input pulse width	t _{TRGW}	1.5	_	t _{Pcyc}	Figure 2.58

Note 1. t_{Pcyc}: PCLK cycle



A/D Converter External Trigger Input Timing Figure 2.58

2.3.5.11 Timing of CAC

Table 2.44 Timing of CAC

Conditions: 1.8 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

	Item		Symbol	Min.	Max.	Unit *1	Test Conditions
CAC	CACREF input pulse width	t _{Pcyc} ≤ t _{cac} *2	t _{CACREF}	4.5 t _{cac} + 3 t _{Pcyc}	—	ns	
		$t_{Pcyc} > t_{cac}^{*2}$		5 t _{cac} + 6.5 t _{Pcyc}			

Note 1. t_{Pcyc} : PCLK cycle Note 2. t_{cac} : CAC count clock source cycle



2.3.5.12 Timing of CLKOUT

Table 2.45Timing of CLKOUT

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

	Item		Symbol	Min.	Max.	Unit *1	Test Conditions
CLKOUT	CLKOUT pin output cycle*3	VCC = 2.7 V or above	t _{Ccyc}	62.5	-	ns	Figure 2.59
		VCC = 1.8 V or above		125			
	CLKOUT pin high pulse width*2	VCC = 2.7 V or above	t _{CH}	15	-	ns	
		VCC = 1.8 V or above		30			
	CLKOUT pin low pulse width*2	VCC = 2.7 V or above	t _{CL}	15	—	ns	
		VCC = 1.8 V or above		30			
	CLKOUT pin output rise time	VCC = 2.7 V or above	t _{Cr}	—	12	ns	
		VCC = 1.8 V or above			25		
	CLKOUT pin output fall time	VCC = 2.7 V or above	t _{Cf}	—	12	ns	1
		VCC = 1.8 V or above			25		

Note 1. t_{Pcyc}: PCLK cycle

Note 2. When the LOCO is selected as the clock output source (the CKOCR.CKOSEL[2:0] bits are 000b), set the clock output division ratio selection to divided by 2 (the CKOCR.CKODIV[2:0] bits are 001b).

Note 3. When the EXTAL external clock input or an oscillator is used with divided by 1 (the CKOCR.CKOSEL[2:0] bits are 010b and the CKOCR.CKODIV[2:0] bits are 000b) to output from CLKOUT, the above should be satisfied with an input duty cycle of 45 to 55%.



Figure 2.59 CLKOUT Output Timing



Timing of CLKOUT_RF 2.3.5.13

Table 2.46 Timing of CLKOUT_RF

Conditions: 1.8 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item	Symbol	Min.	Max.	Unit *1	Test Conditions
	CLKOUT_RF pin output cycle	t _{CRFcyc}	250	_	ns	Figure 2.60
*2	CLKOUT_RF pin high pulse width	t _{CRFH}	100		ns	
	CLKOUT_RF pin low pulse width	t _{CRFL}	100	_	ns	
	CLKOUT_RF pin output rise time	t _{CRFr}	_	5	ns	
_	CLKOUT_RF pin output fall time	t _{CRFf}	_	5	ns	

Note 1.

 $t_{Pcyc}\!\!:$ PCLK cycle The voltage for VCC_RF when CLKOUT_RF pin is to be used is between 3.0 V and 3.6 V. Note 2.



CLKOUT_RF Output Timing Figure 2.60



2.4 USB Characteristics

Table 2.47 USB Characteristics (USB0_DP and USB0_DM Pin Characteristics)

Conditions: $3.0 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} < 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item		Symbol	Min.	Max.	Unit	Test	Conditions
Input	Input high level voltag	je	V _{IH}	2.0	—	V		
characteristics	Input low level voltag	е	V _{IL}	_	0.8	V		
	Differential input sense	sitivity	V _{DI}	0.2		V	USB0_DP - USB0_DM	
	Differential common mode range		V _{CM}	0.8	2.5	V		
Output	Output high level volt	age	V _{OH}	2.8	VCC_USB	V	I _{OH} = -200	μA
characteristics	Output low level volta	ge	V _{OL}	0.0	0.3	V	I _{OL} = 2 mA	
	Cross-over voltage		V _{CRS}	1.3	2.0	V		Figure 2.61,
	Rise time	FS	t _r	4	20	ns		Figure 2.62
		LS		75	300			
	Fall time	FS	t _f	4	20	ns		
		LS		75	300			
	Rise/fall time ratio	FS	t _r /t _f	90	111.11	%	t _r /t _f	
		LS		80	125			
	Output resistance		Z _{DRV}	28	44	Ω	(Adjusting the resistance external elements is not necessary.)	
VBUS	VBUS input voltage		V _{IH}	VCC × 0.8	_	V		
characteristics			V _{IL}	_	VCC × 0.2	V		
Pull-up,	Pull-down resistor		R _{PD}	14.25	24.80	kΩ		
pull-down	Pull-up resistor		R _{PUI}	0.9	1.575	kΩ	During idle	state
			R _{PUA}	1.425	3.09	kΩ	During rece	eption
Battery	D+ sink current		I _{DP_SINK}	25	175	μA		
Charging Specification Ver 1.2	D- sink current		I _{DM_SINK}	25	175	μA		
	DCD source current		I _{DP_SRC}	7	13	μA		
	Data detection voltag	е	V _{DAT_REF}	0.25	0.4	V		
	D+ source current		V _{DP_SRC}	0.5	0.7	V	Output curr	ent = 250 µA
	D- source current		V _{DM_SRC}	0.5	0.7	V	Output curr	ent = 250 µA



Figure 2.61 USB0_DP and USB0_DM Output Timing







2.5 A/D Conversion Characteristics



Figure 2.63 VREFH0 Voltage Range vs. AVCC0

Table 2.48 A/D Conversion Characteristics (1)

Conditions: 2.7 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, 2.7 V ≤ VREFH0 ≤ AVCC0, reference voltage = VREFH0 selected, VSS = AVSS0 = VREFL0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

Item		Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	—	54	MHz	
Resolution			—	12	Bit	
Conversion time* ¹ (Operation at PCLKD = 54 MHz)	Permissible signal source impedance (Max.)	0.83	-	-	μs	High-precision channel The ADCSR.ADHSC bit is 0 The ADSSTRn register is 0Dh
	= 0.3 kΩ	1.33	-	-		Normal-precision channel The ADCSR.ADHSC bit is 0 The ADSSTRn register is 28h
Analog input capacitance	Cs	_	—	15	pF	Pin capacitance included Figure 2.64
Analog input resistance	Rs		—	2.5	kΩ	Figure 2.64
Analog input voltage range	Ain	0	—	VREFH0	V	
Offset error	•		±0.5	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		_	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		_	±0.5	_	LSB	
Absolute accuracy			±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential non-linearity	error	_	±1.0	—	LSB	
INL integral non-linearity erro	r	_	±1.0	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential non-linearity error, and INL integral non-linearity error do not include quantization errors.

Table 2.49 A/D Conversion Characteristics (2)

Conditions: 2.4 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, 2.4 V ≤ VREFH0 ≤ AVCC0, reference voltage = VREFH0 selected, VSS = AVSS0 = VREFL0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

Item		Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	—	32	MHz	
Resolution			—	12	Bit	
Conversion time ^{*1} (Operation at PCLKD = 32 MHz)	Permissible signal source impedance (Max.) = $1.3 \text{ k}\Omega$	1.41	_	_	μs	High-precision channel The ADCSR.ADHSC bit is 0 The ADSSTRn register is 0Dh
		2.25	_	_		Normal-precision channel The ADCSR.ADHSC bit is 0 The ADSSTRn register is 28h
Analog input capacitance	Cs	—	_	15	pF	Pin capacitance included Figure 2.64
Analog input resistance	Rs	_	—	2.5	kΩ	Figure 2.64
Offset error			±0.5	±4.5	LSB	
Full-scale error			±0.75	±4.5	LSB	
Quantization error		_	±0.5	—	LSB	
Absolute accuracy			±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential non-linearity error		_	±1.0	—	LSB	
INL integral non-linearity er	ror	_	±1.0	±4.5	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential non-linearity error, and INL integral non-linearity error do not include quantization errors.



Table 2.50 A/D Conversion Characteristics (3)

Conditions: 2.7 V ≤ VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF ≤ 3.6 V, 2.7 V ≤ VREFH0 ≤ AVCC0, reference voltage = VREFH0 selected, VSS = AVSS0 = VREFL0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

Item		Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	_	27	MHz	
Resolution		_	_	12	Bit	
Conversion time*1 (Operation at PCLKD = 27 MHz)	Permissible signal source impedance (Max.) = 1.1 kΩ	2	μs		μs	High-precision channel The ADCSR.ADHSC bit is 1 The ADSSTRn.SST[7:0] bits are 0Dh
		3	_	_		Normal-precision channel The ADCSR.ADHSC bit is 1 The ADSSTRn.SST[7:0] bits are 28h
Analog input capacitance	Cs		-	15	pF	Pin capacitance included Figure 2.64
Analog input resistance	Rs	_	_	2.5	kΩ	Figure 2.64
Offset error		_	±0.5	±4.5	LSB	
Full-scale error		_	±0.75	±4.5	LSB	
Quantization error		_	±0.5	—	LSB	
Absolute accuracy		—	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential non-linearity error		—	±1.0	-	LSB	
INL integral non-linearity er	ror		±1.0	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential non-linearity error, and INL integral non-linearity error do not include quantization errors.



Table 2.51 A/D Conversion Characteristics (4)

Conditions: $2.4 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC0} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, 2.4 \text{ V} \le \text{VREFH0} \le \text{AVCC0}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = 0 \text{ V}, \text{ reference voltage} = \text{VREFH0 selected}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

Item		Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	_	16	MHz	
Resolution			_	12	Bit	
Conversion time ^{*1} (Operation at PCLKD = 16 MHz)	Permissible signal source impedance (Max.) = $2.2 \text{ k}\Omega$	3.38	_	— — µs	μs	High-precision channel The ADCSR.ADHSC bit is 1 The ADSSTRn register is 0Dh
		5.06	_	_		Normal-precision channel The ADCSR.ADHSC bit is 1 The ADSSTRn register is 28h
Analog input capacitance	Cs	_	-	15	pF	Pin capacitance included Figure 2.64
Analog input resistance	Rs		—	2.5	kΩ	Figure 2.64
Offset error			±0.5	±4.5	LSB	
Full-scale error			±0.75	±4.5	LSB	
Quantization error		_	±0.5	—	LSB	
Absolute accuracy		_	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential non-linearity error		_	±1.0	—	LSB	
INL integral non-linearity er	ror	—	±1.0	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential non-linearity error, and INL integral non-linearity error do not include quantization errors.



Table 2.52 A/D Conversion Characteristics (5)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{USB} = \text{AVCC0} = \text{VCC}_{RF} = \text{AVCC}_{RF} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VREFH0} \le \text{AVCC0}, \text{VSS} = \text{AVSS0} = \text{VSS}_{USB} = 0 \text{ V}, \text{ reference voltage} = \text{VREFH0 selected}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

	_		•		u	
Item		Min.	Тур.	Max.	Unit	Test Conditions
Frequency		1	_	8	MHz	
Resolution			—	12	Bit	
Conversion time*1 (Operation at PCLKD = 8 MHz)	Permissible signal source impedance (Max.) = 5 kΩ	ource impedance Max.) = 5 kΩ		μs	High-precision channel The ADCSR.ADHSC bit is 1 The ADSSTRn register is 0Dh	
		10.13	_	—		Normal-precision channel The ADCSR.ADHSC bit is 1 The ADSSTRn register is 28h
Analog input capacitance	Cs	_	—	15	pF	Pin capacitance included Figure 2.64
Analog input resistance	Rs		—	2.5	kΩ	Figure 2.64
Offset error			±1	±7.5	LSB	
Full-scale error		_	±1.5	±7.5	LSB	
Quantization error		_	±0.5	—	LSB	
Absolute accuracy		_	±3.0	±8.0	LSB	
DNL differential non-linearity error		_	±1.0	—	LSB	
INL integral non-linearity er	ror	—	±1.25	±3.0	LSB	

Note: The characteristics apply when no pin functions other than A/D converter input are used. Absolute accuracy includes quantization errors. Offset error, full-scale error, DNL differential non-linearity error, and INL integral non-linearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. As the test conditions, the number of sampling states is indicated.

Table 2.53 A/D Converter Channel Classification

Classification	Channel	Conditions	Remarks
High-precision channel	AN000 to AN007	AVCC0 = 1.8 to 3.6 V	Pins AN000 to AN007 cannot be used as digital
Normal-precision channel	AN016 to AN020, AN027		outputs when the A/D converter is in use.
Internal reference voltage input channel	Internal reference voltage	AVCC0 = 2.0 to 3.6 V	
Temperature sensor input channel	Temperature sensor output	AVCC0 = 2.0 to 3.6 V	









Figure 2.65 Illustration of A/D Converter Characteristic Terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of analog input voltage (1-LSB width), that can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as an analog input voltage. For example, if 12-bit resolution is used and if reference voltage (VREFH0 = 3.072 V), then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, 1.5 mV, ... are used as analog input voltages.

If analog input voltage is 6 mV, absolute accuracy = ± 5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, although an output code, 008h, can be expected from the theoretical A/D conversion characteristics.

Integral non-linearity error (INL)

The integral non-linearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential non-linearity error (DNL)

The differential non-linearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

An offset error is the difference between a transition point of the ideal first output code and the actual first output code.

Full-scale error

A full-scale error is the difference between a transition point of the ideal last output code and the actual last output code.



2.6 D/A Conversion Characteristics

Table 2.54D/A Conversion Characteristics (1)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}, \text{ Reference voltage} = \text{AVCC0 or AVSS0 selected}$

Item	Min.	Тур.	Max.	Unit	Test Conditions
Resolution	_	—	12	Bit	
Resistive load	30	—		kΩ	
Capacitive load	_	—	50	pF	
Output voltage range	0.35	—	AVCC0 - 0.47	V	
DNL differential non-linearity error	_	±0.5	±2.0	LSB	
INL integral non-linearity error	_	±2.0	±8.0	LSB	
Offset error	_	—	±30	mV	
Full-scale error	_	—	±30	mV	
Output resistance	_	5	—	Ω	
Conversion time	_	—	30	μs	

Table 2.55 D/A Conversion Characteristics (2)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V},$ $T_a = -40 \text{ to } +85^{\circ}\text{C}, \text{ Reference voltage = internal reference voltage selected}$

Item	Min.	Тур.	Max.	Unit	Test Conditions
Resolution	—	—	12	Bit	
Internal reference voltage (Vbgr)	1.36	1.43	1.50	V	
Resistive load	30	_		kΩ	
Capacitive load	—	_	50	pF	
Output voltage range	0.35	_	Vbgr	V	
DNL differential non-linearity error	_	±2.0	±16.0	LSB	
INL integral non-linearity error	_	±8.0	±16.0	LSB	
Offset error	—	_	30	mV	
Output resistance	—	5	—	Ω	
Conversion time	_	_	30	μs	





Figure 2.66 Illustration of D/A Converter Characteristic Terms

Integral non-linearity error (INL)

The integral non-linearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential non-linearity error (DNL)

The differential non-linearity error is the difference between 1-LSB width based on the ideal D/A conversion characteristics and the width of the actually output code.

Offset error

An offset error is the difference between a transition point of the ideal first output code and the actual first output code.

Full-scale error

A full-scale error is the difference between a transition point of the ideal last output code and the actual last output code.



2.7 Temperature Sensor Characteristics

Table 2.56 Temperature Sensor Characteristics

Conditions: 2.0 V \leq VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \leq 3.6 V, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Relative accuracy	—	—	±1.5	—	°C	2.4 V or above
		_	±2.0	—		Below 2.4 V
Temperature slope	—	_	-3.65	—	mV/°C	
Output voltage (25°C)	—	_	1.05	—	V	VCC = 3.3 V
Temperature sensor start time	t _{START}	_	_	5	μs	
Sampling time	_	5	_	—	μs	

2.8 Comparator Characteristics

Table 2.57 Comparator Characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}, \text{T}_a = -40 \text{ to } +85^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
CVREFB2, CVRE	CVREFB2, CVREFB3 input reference voltage		0	—	VCC - 1.4	V	
CMPB2, CMPB3 i	nput voltage	VI	-0.3	—	VCC + 0.3	V	
Offset	Comparator high-speed mode	—	—	—	50	mV	
	Comparator high-speed mode Window function enabled	—	—	—	60	mV	
	Comparator low-speed mode	—	—	—	40	mV	
Comparator output delay time	Comparator high-speed mode	Td	—		1.2	μs	VCC = 3 V, input slew rate ≥ 50 mV/µs
	Comparator high-speed mode Window function enabled	Tdw	_	—	2.0	μs	
	Comparator low-speed mode	Td	—	—	5.0	μs	
High-side reference (comparator high- function enabled)	speed mode, window	VRFH	_	0.76 VCC	_	V	
Low-side reference (comparator high- function enabled)	e voltage speed mode, window	VRFL	_	0.24 VCC	_	V	
Operation stabilization	ation wait time	Tcmp	100	—	—	μs	



Figure 2.67 Comparator Output Delay Time in Comparator High-Speed Mode and Low-Speed Mode





Comparator Output Delay Time in High-Speed Mode with Window Function Enabled

2.9 CTSU Characteristics

Table 2.58 CTSU Characteristics

Conditions: $1.8 V \le VCC = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to $+85^{\circ}C$

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
External capacitance connected to TSCAP pin	C _{tscap}	9	10	11	nF	
TS pin capacitive load	C _{base}		—	50	pF	
Permissible output high current	Σl _{OH}		_	-24	mA	When the mutual capacitance method is applied

2.10 Characteristics of Power-On Reset Circuit and Voltage Detection Circuit

Table 2.59 Characteristics of Power-On Reset Circuit and Voltage Detection Circuit (1)

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_{\text{USB}} = \text{VSS}_{\text{RF}} = 0 \text{ V}, \text{T}_{a} = -40 \text{ to } +85^{\circ}\text{C}$

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Voltage detection	Power-on reset (POR)	V _{POR}	1.35	1.50	1.65	V	Figure 2.69, Figure 2.70
level	Voltage detection circuit	V _{det0_1}	2.70	2.82	3.00	V	Figure 2.71
	(LVD0)*1	V _{det0_2}	2.37	2.51	2.67		At falling edge VCC
		V _{det0_3}	1.80	1.90	1.99		
	Voltage detection circuit (LVD1)* ²	V _{det1_4}	2.99	3.10	3.29	V	Figure 2.72
		V _{det1_5}	2.89	3.00	3.19		At falling edge VCC
		V _{det1_6}	2.79	2.90	3.09		
		V _{det1_7}	2.68	2.79	2.98		
		V _{det1_8}	2.57	2.68	2.87		
		V _{det1_9}	2.47	2.58	2.67		
		V _{det1_A}	2.37	2.48	2.57		
		V _{det1_B}	2.10	2.20	2.30		
		V _{det1_C}	1.86	1.96	2.06		
		V _{det1_D}	1.80	1.86	1.96		

Note: These characteristics apply when noise is not superimposed on the power supply.

Note 1. n in the symbol Vdet0_n denotes the value of the OFS1.VDSEL[1:0] bits.

Note 2. n in the symbol Vdet1_n denotes the value of the LVDLVLR.LVD1LVL[3:0] bits.



Table 2.60 Characteristics of Power-On Reset Circuit and Voltage Detection Circuit (2)

Conditions: $1.8 V \le VCC0 = VCC_USB = AVCC0 = VCC_RF = AVCC_RF \le 3.6 V$, VSS = AVSS0 = VSS_USB = VSS_RF = 0 V, $T_a = -40$ to +85°C

	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Wait time after	At normal startup*1	t _{POR}	—	9.1	_	ms	Figure 2.70
power-on reset cancellation	During fast startup time ^{*2}	t _{POR}	—	1.6	—		
Wait time after voltage monitoring 0 reset cancellation	Power-on voltage monitoring 0 reset disabled*1	t _{LVD0}	—	568	—	μs	Figure 2.71
	Power-on voltage monitoring 0 reset enabled* ²		_	100	_		
Wait time after voltage cancellation	e monitoring 1 reset	t _{LVD1}	—	100		μs	Figure 2.72
Response delay time		t _{det}	—	—	350	μs	Figure 2.69
Minimum VCC down time*3		t _{VOFF}	350	—	—	μs	Figure 2.69, VCC = 1.0 V or above
Power-on reset enabl	e time	t _{W(POR)}	1			ms	Figure 2.70, VCC = below 1.0 V
LVD operation stabiliz enabled)	ation time (after LVD is	Td _(E-A)	—		300	μs	Figure 2.72
Hysteresis width (pow	ver-on rest (POR))	V _{PORH}	—	110	—	mV	
Hysteresis width (volt	age detection circuit:	V _{LVH}	—	70		mV	When Vdet1_4 is selected
LVD1)				60	—		When Vdet1_5 to Vdet1_9 is selected
				50			When Vdet1_A or Vdet1_B is selected
			—	40	—		When Vdet1_C or Vdet1_D is selected

Note: These characteristics apply when noise is not superimposed on the power supply.

Note 1. When OFS1.(LVDAS, FASTSTUP) = 11b.

Note 2. When OFS1.(LVDAS, FASTSTUP) ≠ 11b.

Note 3. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR}, V_{det0}, and V_{det1} for the POR/LVD.



Figure 2.69 Voltage Detection Reset Timing



Figure 2.70 Power-On Reset Timing



Figure 2.71 Voltage Detection Circuit Timing (Vdet0)





Figure 2.72 Voltage Detection Circuit Timing (V_{det1})

2.11 Oscillation Stop Detection Timing

Table 2.61 Oscillation Stop Detection Timing

```
Conditions: 1.8 V \le VCC = VCC\_USB = AVCC0 = VCC\_RF = AVCC\_RF \le 3.6 V,
VSS = AVSS0 = VREFL0 = VSS_USB = VSS\_RF = 0 V, T<sub>a</sub> = -40 to +85°C
```

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Detection time	t _{dr}	—	_	1	ms	Figure 2.73



Figure 2.73 Oscillation Stop Detection Timing

2.12 Battery Backup Function Characteristics

Table 2.62 Battery Backup Function Characteristics

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_{\text{USB}} = \text{AVCC0} = \text{VCC}_{\text{RF}} = \text{AVCC}_{\text{RF}} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le \text{VBATT} \le 3.6 \text{ V}, 1.8 \text{ V} \le 1.8 \text{ V} = 1.8 \text{ V} \le 1.8 \text{ V} \le 1.8 \text{ V} = 1.8 \text{ V}$

VSS = AVSS0 = VREFL0 = VSS_USB = VSS_RF = 0 V, T_a = -40 to +85°C

Item	Item			Тур.	Max.	Unit	Test Conditions
Voltage level for switching to bat	V _{DETBATT}	1.99	2.09	2.19	V	Figure 2.74	
Hysteresis width	V _{VBATTH}	_	100	—	mV		
VCC-off period for starting powe	t _{VOFFBATT}		—	350	μs		
Allowable voltage change rising/	Allowable voltage change rising/falling gradient		1.0	—	—	ms/V	Figure 2.7
Level for detection of voltage	VBTLVDLVL[1:0] = 10b	V _{DETBATLVD}	2.11	2.20	2.29	V	Figure 2.74
drop on the VBATT pin (falling)	VBTLVDLVL[1:0] = 11b		1.87	2.00	2.13	V	
Hysteresis width for detection of voltage drop on the VBATT pin		V _{BATLVDH}	—	50	—	mV	

Note: The VCC-off period for starting power supply switching indicates the period in which VCC is below the minimum value of the voltage level for switching to battery backup (V_{DETBATT}).



Figure 2.74 Battery Backup Function Characteristics



2.13 ROM (Flash Memory for Code Storage) Characteristics

Table 2.63	ROM (Flash Memory for Code Storage) Characteristics (1)
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	Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Reprogramming/er	asure cycle* ¹	N _{PEC}	1000			Times	
Data hold time	After 1000 times of N_{PEC}	t _{DRP}	20*2, *3			Year	T _a = +85°C

Note 1. Definition of reprogram/erase cycle: The reprogram/erase cycle is the number of erasing for each block. When the reprogram/ erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 4-byte programming is performed 256 times for different addresses in a 1-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided from Renesas Electronics. Note 3. This result is obtained from reliability testing.

Table 2.64 ROM (Flash Memory for Code Storage) Characteristics (2) High-Speed Operating Mode

Conditions: $2.7 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = 0 \text{ V}$ Temperature range for the programming/erasure operation: $T_a = -40$ to $+85^{\circ}\text{C}$

Item		Cumbal	F	CLK = 1 M⊦	lz	F	CLK = 32 MI	Ηz	Unit
item		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Programming time	8-byte	t _{P8}	—	112	967	—	52.3	491	μs
Erasure time	2-Kbyte	t _{E2K}	—	8.75	278	—	5.50	215	ms
	512-Kbyte (when block erase command is used)	t _{E512K}	_	928	19218	_	72.0	1679	ms
	512-Kbyte (when all- block erase command is used)	t _{EA512K}	_	923	19013	_	66.7	1469	ms
Blank check time	8-byte	t _{BC8}	—	—	55.0	_	—	16.1	μs
	2-Kbyte	t _{BC2K}	—	—	1840	—	—	136	ms
Erase operation forced	Erase operation forced stop time		—	—	18.0	—	—	10.7	μs
Start-up area switching setting time		t _{SAS}	—	12.3	566.5		6.2	434	ms
Access window time		t _{AWS}	—	12.3	566.5	_	6.2	434	ms
ROM mode transition wait time 1		t _{DIS}	2.0	—	—	2.0	—	—	μs
ROM mode transition	wait time 2	t _{MS}	5.0	—	—	5.0	—	—	μs

Note:The time until each operation of the flash memory is started after instructions are executed by software is not included.Note:The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below

4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be within ±3.5%.



Table 2.65 ROM (Flash Memory for Code Storage) Characteristics (3) Middle-Speed Operating Mode

Conditions: $1.8 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}$ Temperature range for the programming/erasure operation: $T_a = -40$ to $+85^{\circ}\text{C}$

Item		Symbol	F	CLK = 1 M⊦	lz	F	CLK = 8 MH	lz	Unit
item		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Onic
Programming time	8-byte	t _{P8}	—	152	1367	—	97.9	936	μs
Erasure time	2-Kbyte	t _{E2K}	—	8.8	279.7	—	5.9	221	ms
	512-Kbyte (when block erase command is used)	t _{E512K}	_	928	19221	_	191	4108	ms
	512-Kbyte (when all- block erase command is used)	t _{EA512K}	_	923	19015		185	3901	ms
Blank check time	8-byte	t _{BC8}	—	—	85.0	_	—	50.88	μs
	2-Kbyte	t _{BC2K}	—	—	1870	—	—	402	μs
Erase operation forced	Erase operation forced stop time		—	—	28.0	—	—	21.3	μs
Start-up area switching setting time		t _{SAS}	—	13.0	573.3	—	7.7	451	ms
Access window time		t _{AWS}	—	13.0	573.3	—	7.7	451	ms
ROM mode transition wait time 1		t _{DIS}	2.0	—	—	2.0	—	—	μs
ROM mode transition w	/ait time 2	t _{MS}	3.0	—	—	3.0	—	—	μs

Note:The time until each operation of the flash memory is started after instructions are executed by software is not included.Note:The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below

4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set. Note: The frequency accuracy of FCLK must be within ±3.5%.



2.14 E2 DataFlash Characteristics (Flash Memory for Data Storage)

	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	
Reprogramming/erasure cycle*1		N _{DPEC}	100000	1000000		Times	
Data hold time	After 10000 times of N _{DPEC}	t _{DDRP}	20* ^{2, *3}	—	_	Year	T _a = +85°C
	After 100000 times of N _{DPEC}		5* ^{2, *3}	—	_	Year	
	After 1000000 times of N _{DPEC}		—	1*2, *3	_	Year	T _a = +25°C

Table 2.66 E2 DataFlash Characteristics (1)

Note 1. The reprogram/erase cycle is the number of erasing for each block. When the reprogram/erase cycle is n times (n = 100000), erasing can be performed n times for each block. For instance, when 1-byte programming is performed 1000 times for different addresses in a 1-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).

Note 2. Characteristic when the flash memory programmer is used and the self-programming library is provided from Renesas Electronics.

Note 3. These results are obtained from reliability testing.

Table 2.67 E2 DataFlash Characteristics (2): high-speed operating mode

Conditions: $2.7 \text{ V} \le \text{VCC} = \text{VCC}_\text{USB} = \text{AVCCO} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}, \text{VSS} = \text{AVSSO} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}$ Temperature range for the programming/erasure operation: $T_a = -40$ to $+85^{\circ}\text{C}$

Itom	Item		FCL	K = 1 MHz		FCLK	Unit		
nem		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Programming time	1 byte	t _{DP1}	—	95.0	797	—	40.8	376	μs
Erasure time	1 Kbyte	t _{DE1K}	—	19.5	498	—	6.2	230	ms
	8 Kbyte	t _{DE8K}	—	119.8	2556	—	12.9	368	ms
Blank check time	1 byte	t _{DBC1}	—	—	55.00	—	—	16.1	μs
	1 Kbyte	t _{DBC1K}	—	—	0.72	—	—	0.50	ms
Erase operation forced stop time		t _{DSED}	—	—	16.0	—	—	10.7	μs
DataFlash STOP recovery time		t _{DSTOP}	5.0	_	_	5.0	_		μs

Note:The time until each operation of the flash memory is started after instructions are executed by software is not included.Note:The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below
4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be within $\pm 3.5\%$.

Table 2.68 E2 DataFlash Characteristics (3): middle-speed operating mode

Conditions: $1.8 \text{ V} \le \text{VCC0} = \text{VCC}_\text{USB} = \text{AVCC0} = \text{VCC}_\text{RF} = \text{AVCC}_\text{RF} \le 3.6 \text{ V}$, $\text{VSS} = \text{AVSS0} = \text{VSS}_\text{USB} = \text{VSS}_\text{RF} = 0 \text{ V}$ Temperature range for the programming/erasure operation: $T_a = -40$ to $+85^{\circ}\text{C}$

ltom	Item		FCL	K = 1 MHz		FCL	Unit		
nem		Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Programming time	1 byte	t _{DP1}	—	135	1197	—	86.5	823	μs
Erasure time	1 Kbyte	t _{DE1K}	—	19.6	501	—	8.0	265	ms
	8 Kbyte	t _{DE8K}	—	120	2558	—	27.7	669	ms
Blank check time	1 byte	t _{DBC1}	—	—	85.0	—	—	50.9	μs
	1 Kbyte	t _{DBC1K}	—	—	0.72	—	—	1.45	ms
Erase operation forced stop time		t _{DSED}	—	—	28.0	—	—	21.3	μs
DataFlash STOP recor	very time	t _{DSTOP}	0.72	—	—	0.72	—	—	μs

Note:The time until each operation of the flash memory is started after instructions are executed by software is not included.Note:The lower-limit frequency of FCLK is 1 MHz during programming or erasing of the flash memory. When using FCLK at below
4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be within ±3.5%.



2.15 BLE Characteristics

2.15.1 Transmission Characteristics

Table 2.69 Transmission Characteristics

Conditions: VCC = VCC_RF = AVCC_RF = 3.3 V, VSS = VSS_RF = 0 V, T_a = $+25^{\circ}$ C

Item		Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Range of frequency	RF _{CF}	2402	—	2480	MHz		
Data rate		RF _{DATA_2M}	—	2	—	Mbps	
		RF _{DATA_1M}	—	1	—	Mbps	
		RF _{DATA_500k}	—	500	—	kbps	
		RF _{DATA_125k}	—	125	—	kbps	
Maximum transmitted o	utput power	RF _{POWER}	—	0	2	dBm	0 dBm output mode
			—	4	6	dBm	4 dBm output mode
Output frequency error 85-pin BGA, 56-pin QFN		RF _{TXFERR}	-10	—	10	ppm	*1
83-pin LGA		RF _{MTXFERR}	-50	—	50	ppm	T _a : –40 to +85°C

Note: The characteristics are based on pins and functions other than those for the BLE interface not being in use.

Note 1. This does not take frequency errors due to manufacturing irregularities, drift with temperature, or deterioration of the crystal over time into account.

2.15.2 Reception Characteristics (2 Mbps)

Table 2.70 Reception Characteristics

Conditions: VCC = VCC_RF = AVCC_RF = 3.3 V, VSS = VSS_RF = 0 V, T_a = $+25^{\circ}$ C

		1		1	r	1	
Item	Symbol	Min.	Тур.	Max.	Unit	Tes	t Conditions
Input frequency	RF _{RXFIN_2M}	2402	—	2480	MHz		
Maximum input level	RF _{LEVL_2M}	-10	4	—	dBm	*1	
Receiver sensitivity	RF _{STY_2M}	—	-92	—	dBm	*1	
Secondary emission strength	RF _{RXSP_2M}	—	-72	-57	dBm	30 MHz to 1 GHz	
		_	-54	-47	dBm	1 GHz to 12 GHz	
Co-channel rejection ratio	RF _{CCR_2M}	—	-8	—	dB	Prf = -67 dBm*1	
Adjacent channel rejection	RF _{ADCR_2M}	_	2	—	dB	Prf = -67 dBm*1	±2 MHz
ratio		_	35	—	dB		±4 MHz
		_	39	—	dB	-	±6 MHz
Blocking	RF _{BLK_2M}	—	-1	—	dBm	Prf =67 dBm*1	30 MHz to 2000 MHz
		_	-25	—	dBm		2000 MHz to 2399 MHz
		_	-21	—	dBm		2484 MHz to 3000 MHz
		_	-10	—	dBm		> 3000 MHz
Allowable frequency deviation* ²	RF _{RXFER_2M}	-120		120	ppm	*1	
RSSI accuracy	RF _{RSSIS_2M}	—	±4	—	dB	–70 dBm ≤ Prf ≤ -	-10 dBm

Note: The characteristics are based on pins and functions other than those for the BLE interface not being in use.

Note 1. PER ≤ 30.8%, and a 37-byte payload

Note 2. Allowable range of difference between the center frequency for the RF input signals and the carrier frequency generated within the chip

2.15.3 Reception Characteristics (1 Mbps)

Table 2.71 Reception Characteristics

Conditions: VCC = VCC_RF = AVCC_RF = 3.3 V, VSS = VSS_RF = 0 V, T_a = +25°C

Item	Symbol	Min.	Тур.	Max.	Unit	Tes	t Conditions
Input frequency	RF _{RXFIN_1M}	2402	—	2480	MHz		
Maximum input level	RF _{LEVL_1M}	-10	4	_	dBm	*1	
Receiver sensitivity	RF _{STY_1M}		-95	—	dBm	*1	
Secondary emission strength	RF _{RXSP_1M}	_	-72	-57	dBm	30MHz to 1GHz	
		_	-54	-47	dBm	1GHz to 12GHz	
Co-channel rejection ratio	RF _{CCR_1M}	_	-7	—	dB	Prf =67dBm*1	
Adjacent channel rejection ratio	RF _{ADCR_1M}	_	-1	—	dB	$Prf = -67 dBm^{*1}$	±1MHz
			34	—	dB		±2MHz
			35	_	dB		±3MHz
Blocking	RF _{BLK_1M}		0	—	dBm	Prf =67dBm*1	30MHz to 2000MHz
			-24	—	dBm		2000MHz to 2399MHz
			-20	_	dBm		2484MHz to 3000MHz
		—	-4	—	dBm	1	> 3000MHz
Allowable frequency deviation*2	RF _{RXFER_1M}	-120	—	120	ppm	*1	•
RSSI accuracy	RF _{RSSIS_1M}		±4	—	dB	-70 dBm \leq Prf \leq -10 dBm	

Note: The characteristics are based on pins and functions other than those for the BLE interface not being in use.

Note 1. $PER \le 30.8\%$, and a 37-byte payload

Note 2. Allowable range of difference between the center frequency for the RF input signals and the carrier frequency generated within the chip

2.15.4 Reception Characteristics (500 kbps)

Table 2.72 Reception Characteristics

Conditions: VCC = VCC RF = AVCC RF = 3.3 V, VSS = VSS RF = 0 V, T_a = +25°C

Item	Symbol	Min.	Тур.	Max.	Unit	Tes	t Conditions
Input frequency	RF _{RXFIN_500k}	2402	—	2480	MHz		
Maximum input level	RF _{LEVL_500k}	-10	4	—	dBm	*1	
Receiver sensitivity	RF _{STY_500k}		-100	_	dBm	*1	
Secondary emission strength	RF _{RXSP_500k}		-72	-57	dBm	30MHz to 1GHz	
			-54	-47	dBm	1GHz to 12GHz	
Co-channel rejection ratio	RF _{CCR_500k}	_	-4	—	dB	$Prf = -72dBm^{*1}$	
Adjacent channel rejection ratio	RF _{ADCR_500k}		6	—	dB	$Prf = -72dBm^{*1}$	±1MHz
			36	_	dB	-	±2MHz
			42	_	dB	-	±3MHz
Blocking	RF _{BLK_500k}		0	—	dBm	$Prf = -72dBm^{*1}$	30MHz to 2000MHz
			-23	_	dBm	-	2000MHz to 2399MHz
			-20	—	dBm	-	2484MHz to 3000MHz
		_	-7	—	dBm		> 3000MHz
Allowable frequency deviation*2	RF _{RXFER_500k}	-120	—	120	ppm	*1	•
RSSI accuracy	RF _{RSSIS_500k}		±4		dB	–70dBm ≤ Prf ≤ –	-10dBm

Note: The characteristics are based on pins and functions other than those for the BLE interface not being in use.

Note 1. $PER \le 30.8\%$, and a 37-byte payload

Note 2. Allowable range of difference between the center frequency for the RF input signals and the carrier frequency generated within the chip



2.15.5 Reception Characteristics (125 kbps)

Table 2.73 Reception Characteristics

Conditions: VCC = VCC_RF = AVCC_RF = 3.3 V, VSS = VSS_RF = 0 V, T_a = +25°C

—	—		_		u		
Item	Symbol	Min.	Тур.	Max.	Unit	Tes	t Conditions
Input frequency	RF _{RXFIN_125k}	2402	_	2480	MHz		
Maximum input level	RF _{LEVL_125k}	-10	4	—	dBm	*1	
Receiver sensitivity	RF _{STY_125k}	-	-105	—	dBm	*1	
Secondary emission strength	RF _{RXSP_125k}	_	-72	-57	dBm	30 MHz to 1 GHz	
		_	-54	-47	dBm	1 GHz to 12 GHz	
Co-channel rejection ratio	RF _{CCR_125k}	-	-2	—	dB	Prf = -79 dBm*1	
Adjacent channel rejection ratio	RF _{ADCR_125k}	-	12	—	dB	Prf = -79 dBm*1	±1 MHz
		-	39	—	dB	-	±2 MHz
		-	45	—	dB	-	±3 MHz
Blocking	RF _{BLK_125k}	-	0	—	dBm	Prf = -79 dBm*1	30 MHz to 2000 MHz
		-	-23	—	dBm	-	2000 MHz to 2399 MHz
		-	-20	—	dBm	-	2484 MHz to 3000 MHz
		-	-1	—	dBm	-	> 3000MHz
Allowable frequency deviation*2	RF _{RXFER_125k}	-120	—	120	ppm	*1	
RSSI accuracy	RF _{RSSIS_125k}	—	±4	—	dB	–70 dBm ≤ Prf ≤	–10 dBm

Note: The characteristics are based on pins and functions other than those for the BLE interface not being in use.

Note 1. PER ≤ 30.8%, and a 37-byte payload

Note 2. Allowable range of difference between the center frequency for the RF input signals and the carrier frequency generated within the chip



2.16 Usage Notes

2.16.1 Connecting VCL Capacitor and Bypass Capacitors

This MCU integrates an internal voltage-down circuit, which is used for lowering the power supply voltage in the internal MCU automatically to the optimum level. A 4.7- μ F capacitor needs to be connected between this internal voltage-down power supply (VCL pin) and the VSS pin. Place an external capacitor close to the pins. Do not apply the power supply voltage to the VCL pin.

Insert a multilayer ceramic capacitor as a bypass capacitor between each pair of the power supply pins. Implement a bypass capacitor as closer to the MCU power supply pins as possible. We recommend capacitors with a value of 2.2 μ F for that connected to the VCC_RF pin and 0.1 μ F for the others. For the capacitors related to crystal oscillation, see section 9, Clock Generation Circuit in the User's Manual: Hardware. For the capacitors related to analog modules, also see section 44, 12-Bit A/D Converter (S12ADE) in the User's Manual: Hardware.

For notes on designing the printed circuit board, see the descriptions of the application note, the Hardware Design Guide (R01AN1411EJ). The latest version can be downloaded from the Renesas Electronics website.



Appendix 1. Package Dimensions

Information on the latest version of the package dimensions or mountings has been displayed in "Packages" on Renesas Electronics Corporation website.



Figure A 85-Pin BGA (PTBG0085KB-A)





Figure B 83-Pin LGA (PTLG0083KA-A) (1/2)





Figure B 83-Pin LGA (PTLG0083KA-A) (2/2)





Figure C 83-Pin LGA (PTLG0083KA-B) (1/2)





Figure C 83-Pin LGA (PTLG0083KA-B) (2/2)





Figure D 56-Pin QFN (PVQN0056LA-A)



REVISION HISTORY

RX23W Group Datasheet

Classifications

- Items with Technical Update document number: Changes according to the corresponding issued Technical Update

- Items without Technical Update document number: Minor changes that do not require Technical Update to be issued

Rev.	Date		Description	Classification
Nev.	Date	Page	Summary	Classification
1.00	Aug 06, 2019	_	First edition, issued	
1.10	Mar 30, 2021	Features	·	
		1	83-pin LGA specifications, added	
		1. Overview	·	
		All	83-pin LGA specifications, added	
		2. Electrical	Characteristics	
		49	Table 2.24 Clock Timing Note 6, changed	TN-RX*-A0245A/E
		58 to 78	2.3.5 Timing of On-Chip Peripheral Modules, Layout changed	
		Appendix 1.	8	
		105	Figure B 83-Pin HWQFN (PTLG0083KA-A), added	
1.20	Apr 20, 2023	Features		
		1	Package, added	
		1. Overview		
		3	Table 1.1 Outline of Specifications (2/5), changed	TN-RX*-A0265A/E
		6	Table 1.1 Outline of Specifications (5/5), changed	
		8	Table 1.3 List of Products: D Version ($T_a = -40$ to +85°C), changed	
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General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power is supplied until the power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a systemevaluation test for the given product.

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